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Yu et al.

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(54) **STRUCTURE AND PROCESS FOR
PHOTONIC PACKAGES**

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Related U.S. Application Data

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16, 2021, now Pat. No. 12,135,454.

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G02B 6/12 (2006.01)

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2006/12173 (2013.01); **G02B 2006/12176**
(2013.01)

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G02B 2006/1213; G02B 2006/12173;
G02B 2006/12176
See application file for complete search history.

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Primary Examiner — Tina Wong

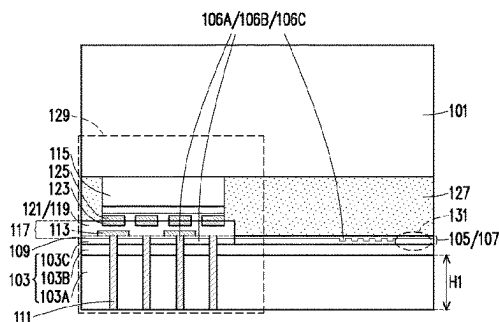
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(57) **ABSTRACT**

Semiconductor devices and methods of forming the semiconductor devices are described herein. A method includes providing a first material layer between a second material layer and a semiconductor substrate and forming a first waveguide in the second material layer. The method also includes forming a photonic die over the first waveguide and forming a first cavity in the semiconductor substrate and exposing the first layer. Once formed, the first cavity is filled with a first backfill material adjacent the first layer. The methods also include electrically coupling an electronic die to the photonic die. Some methods include packaging the semiconductor device in a packaged assembly.

20 Claims, 27 Drawing Sheets

300



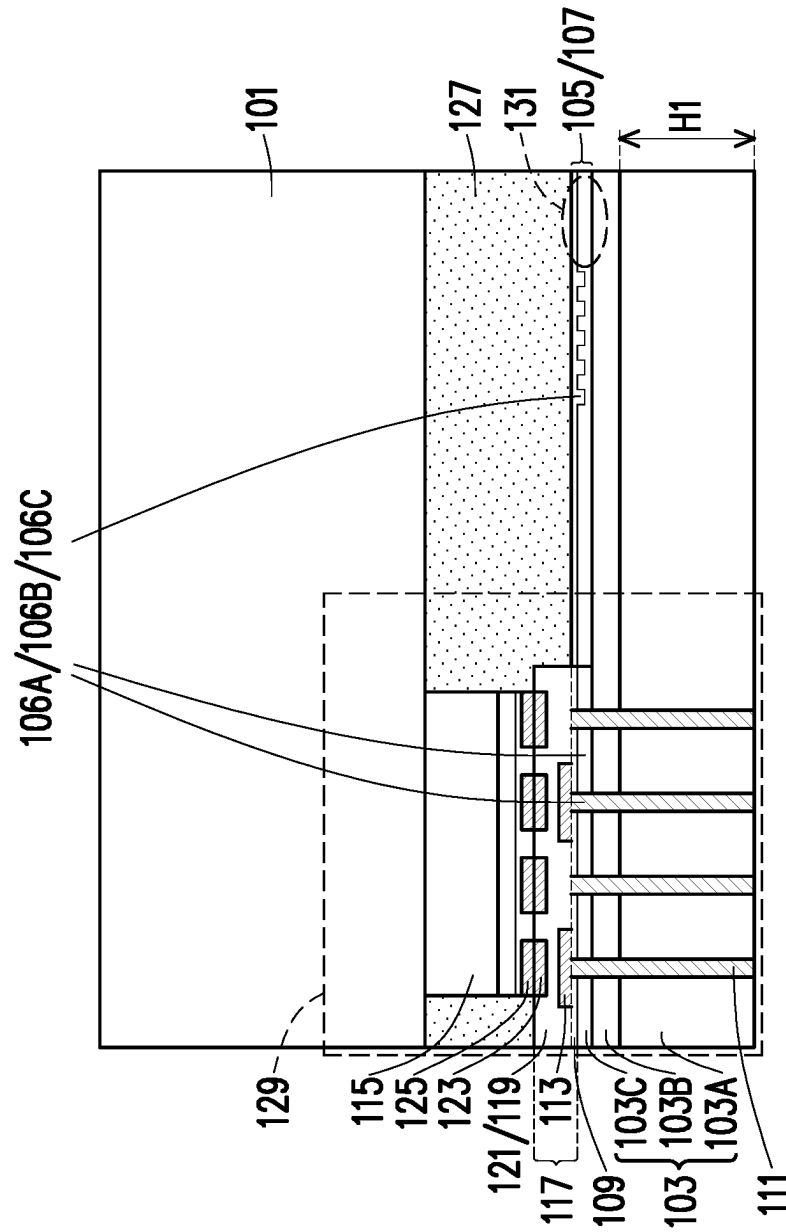


FIG. 1A

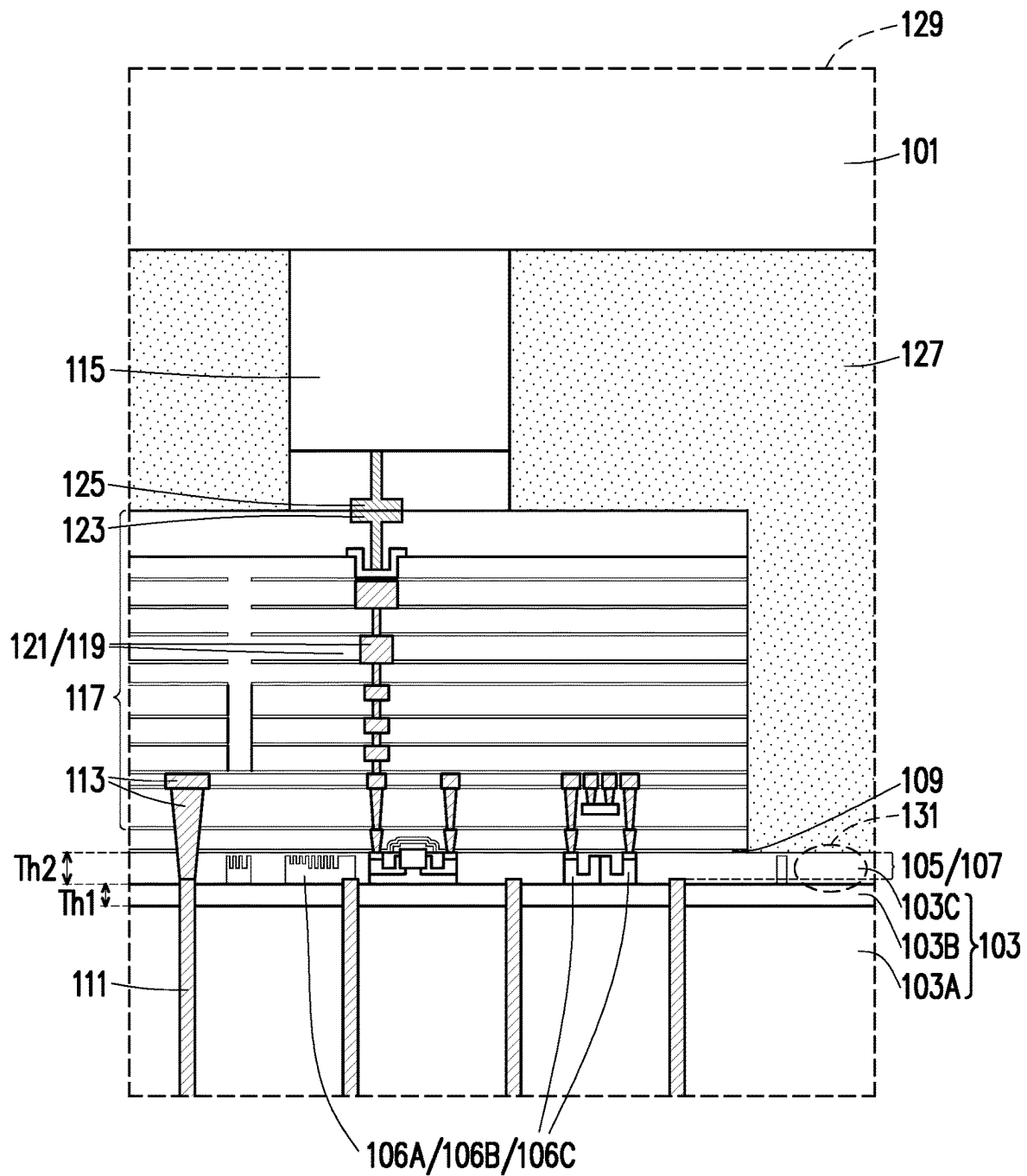


FIG. 1B

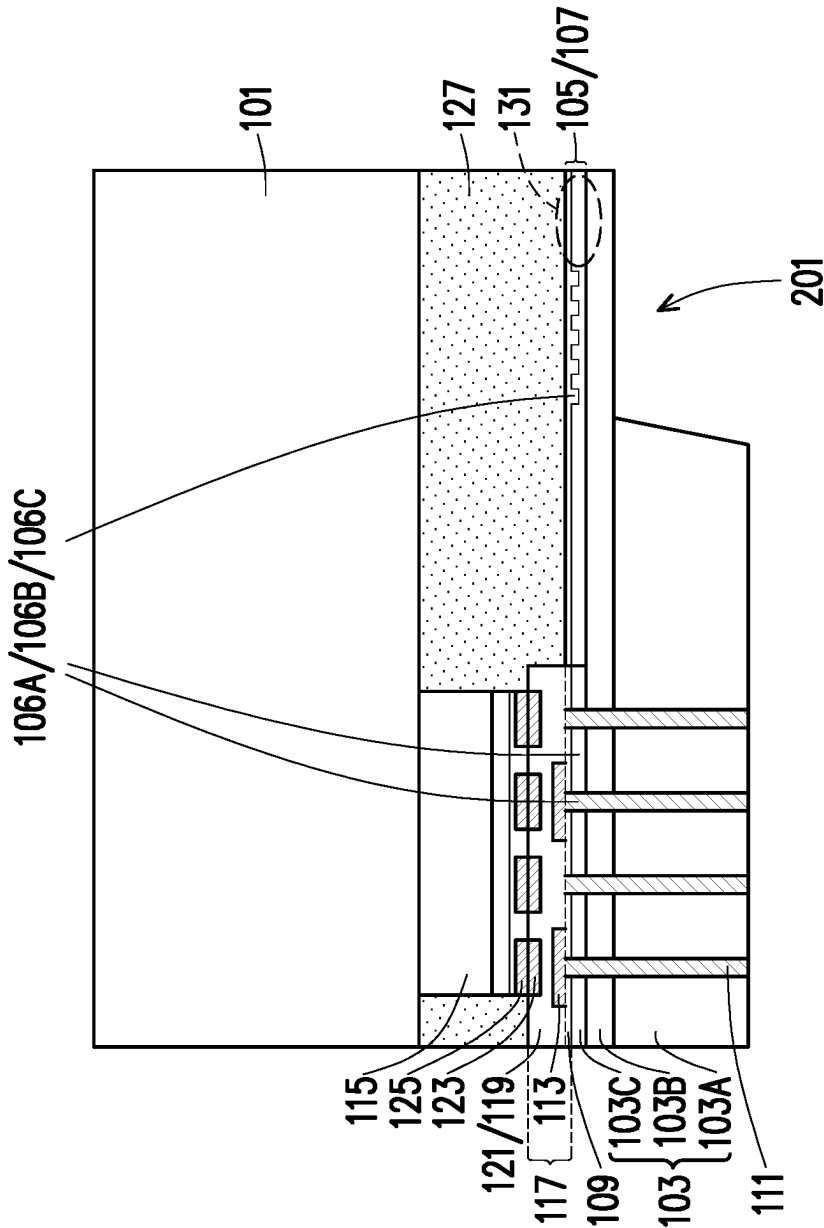


FIG. 2

300

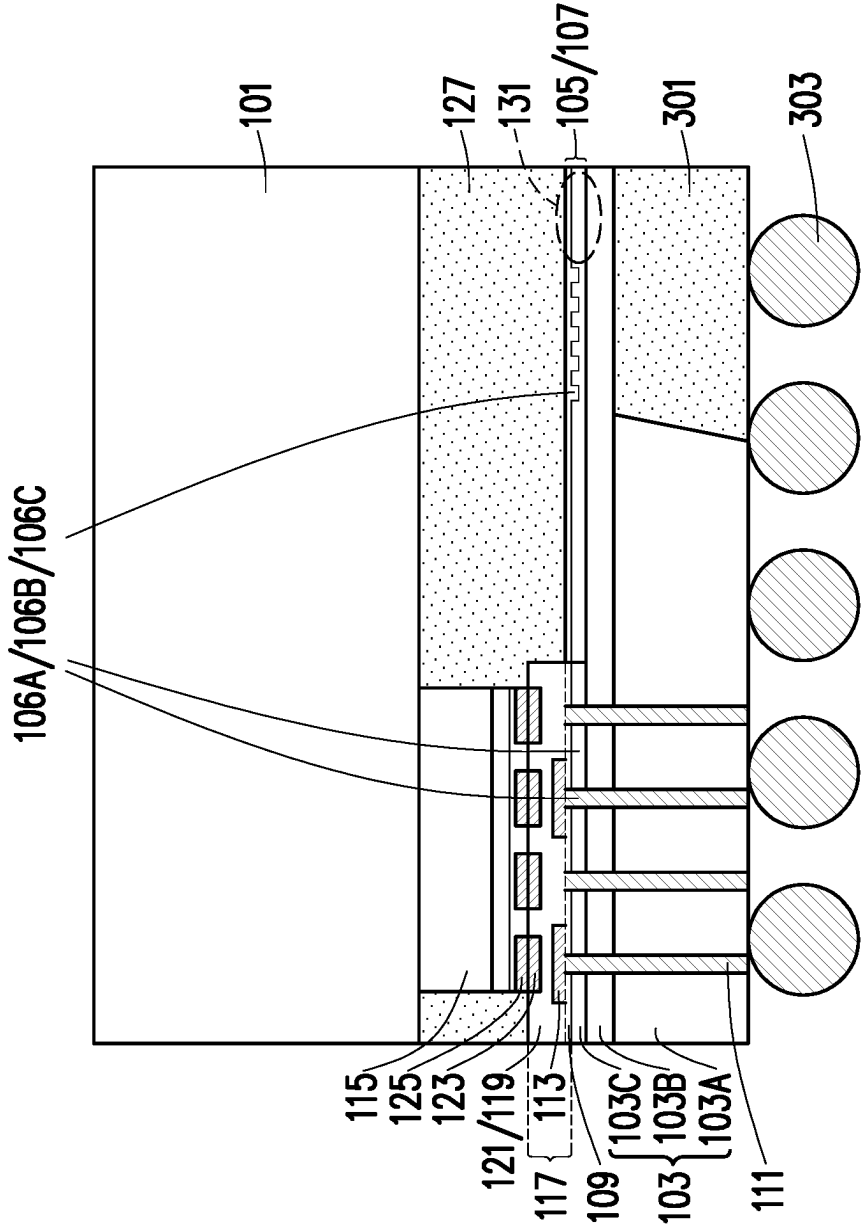


FIG. 3

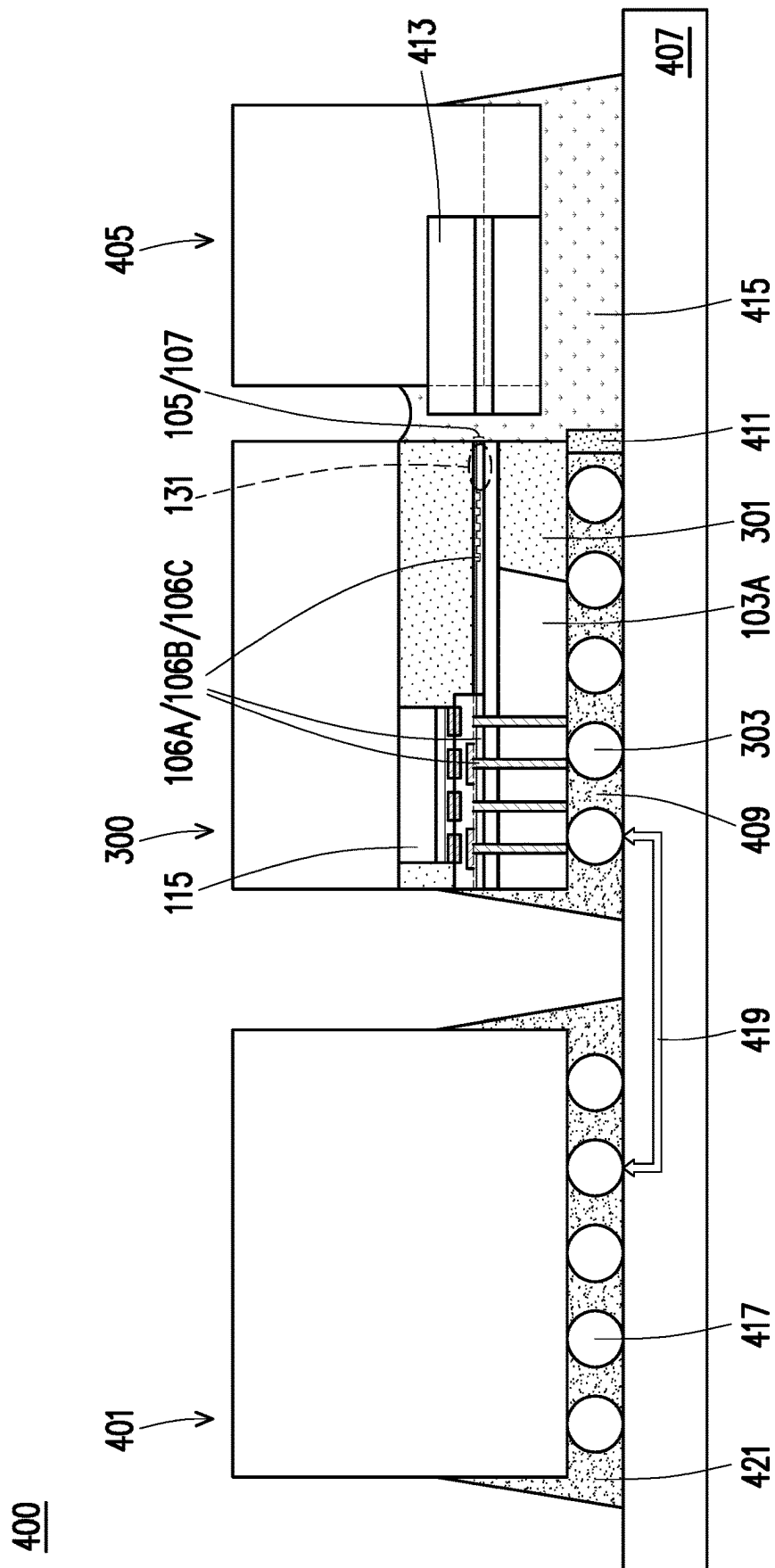


FIG. 4

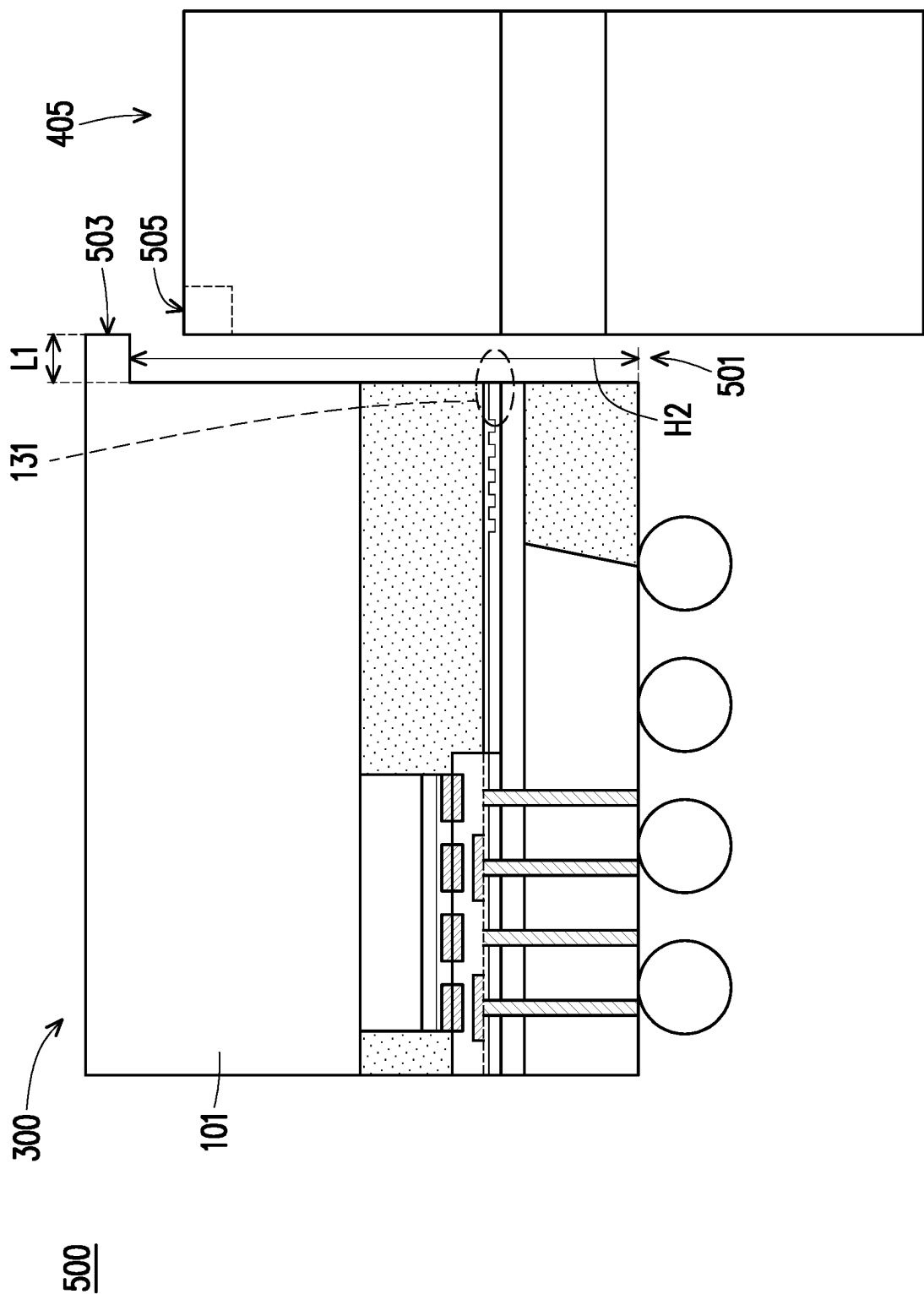


FIG. 5

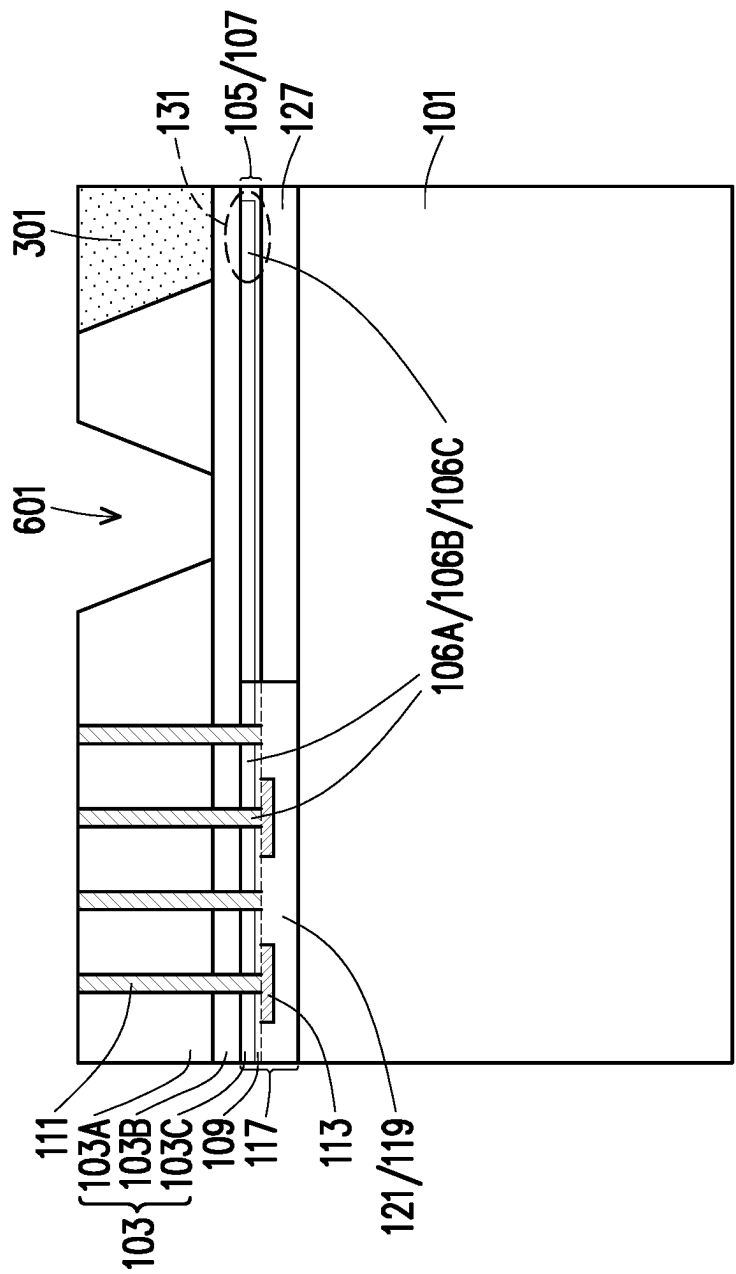


FIG. 6

700

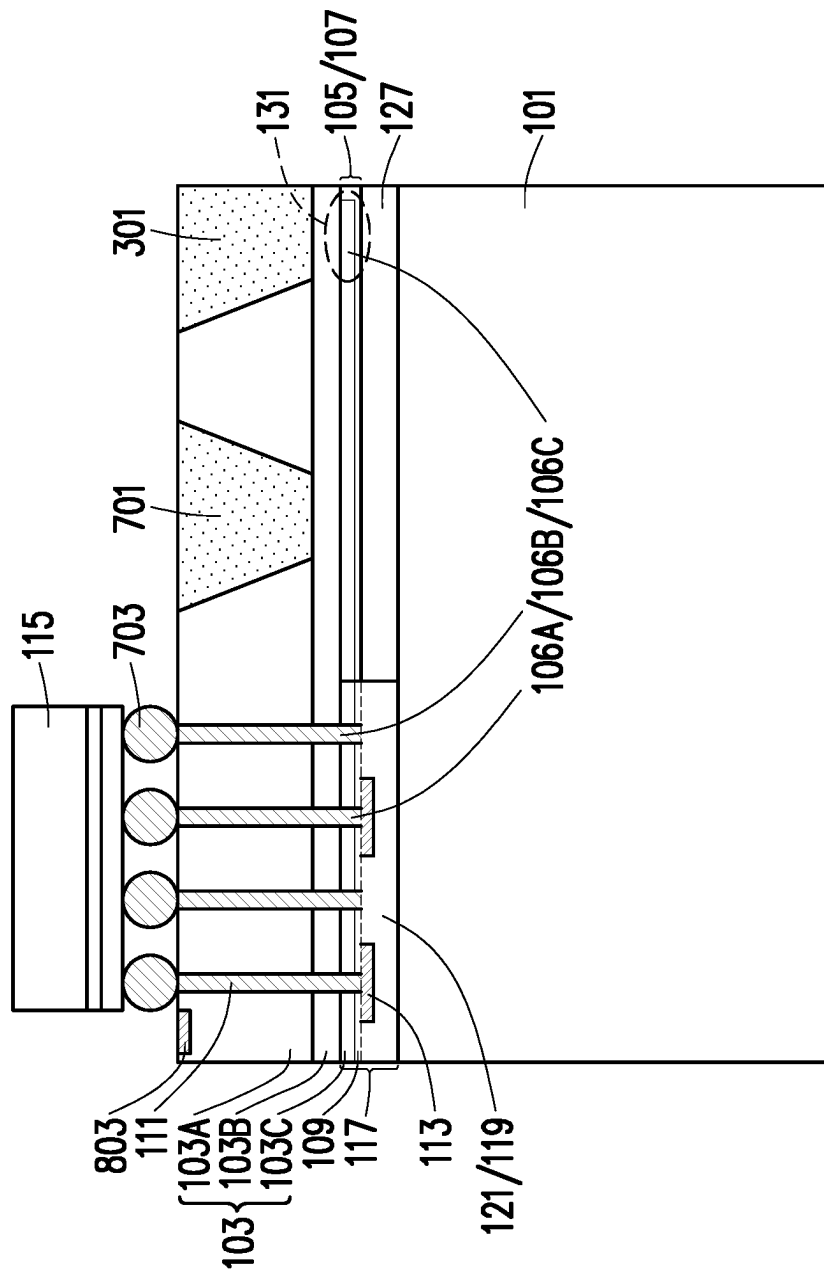
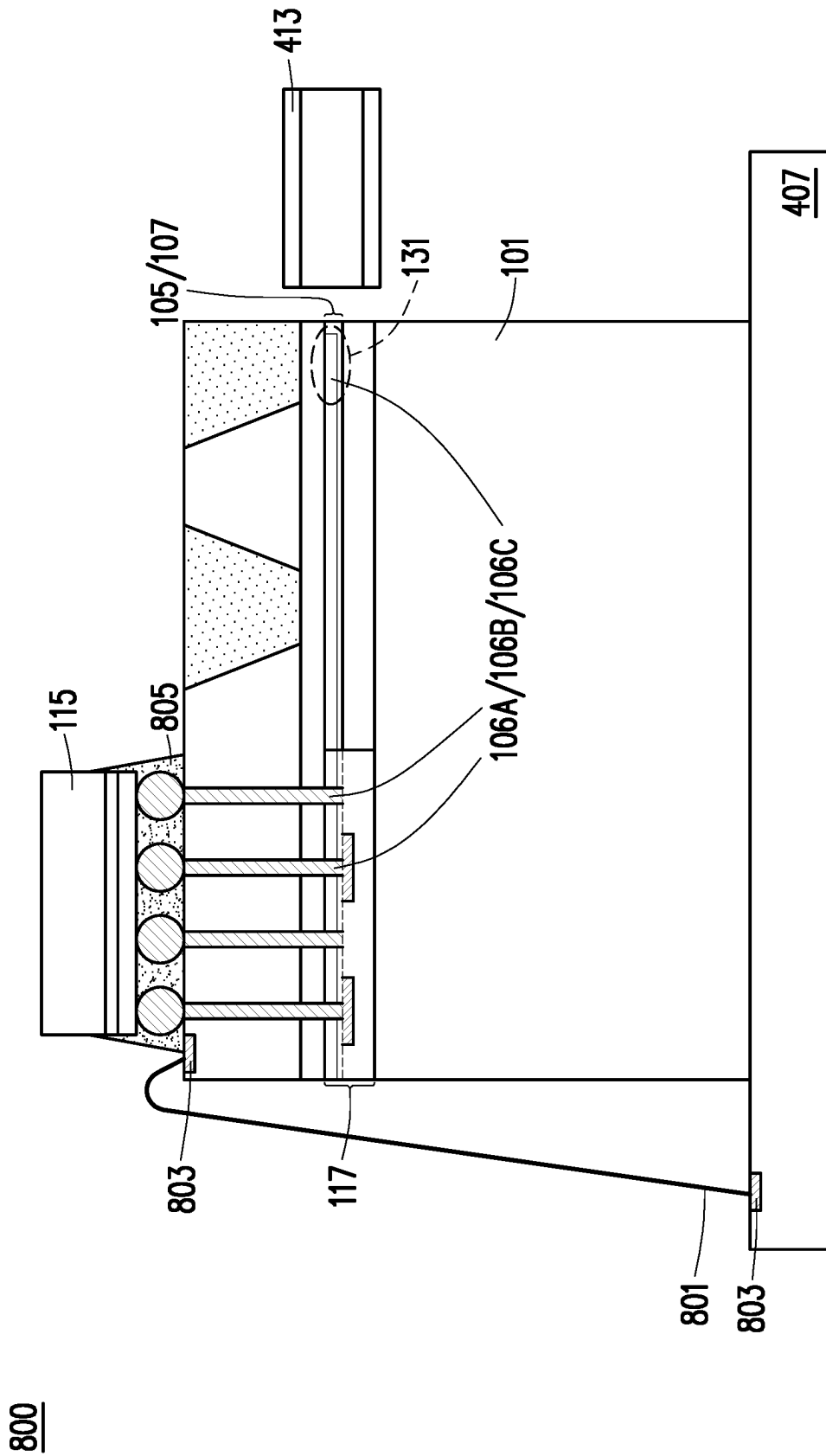


FIG. 7



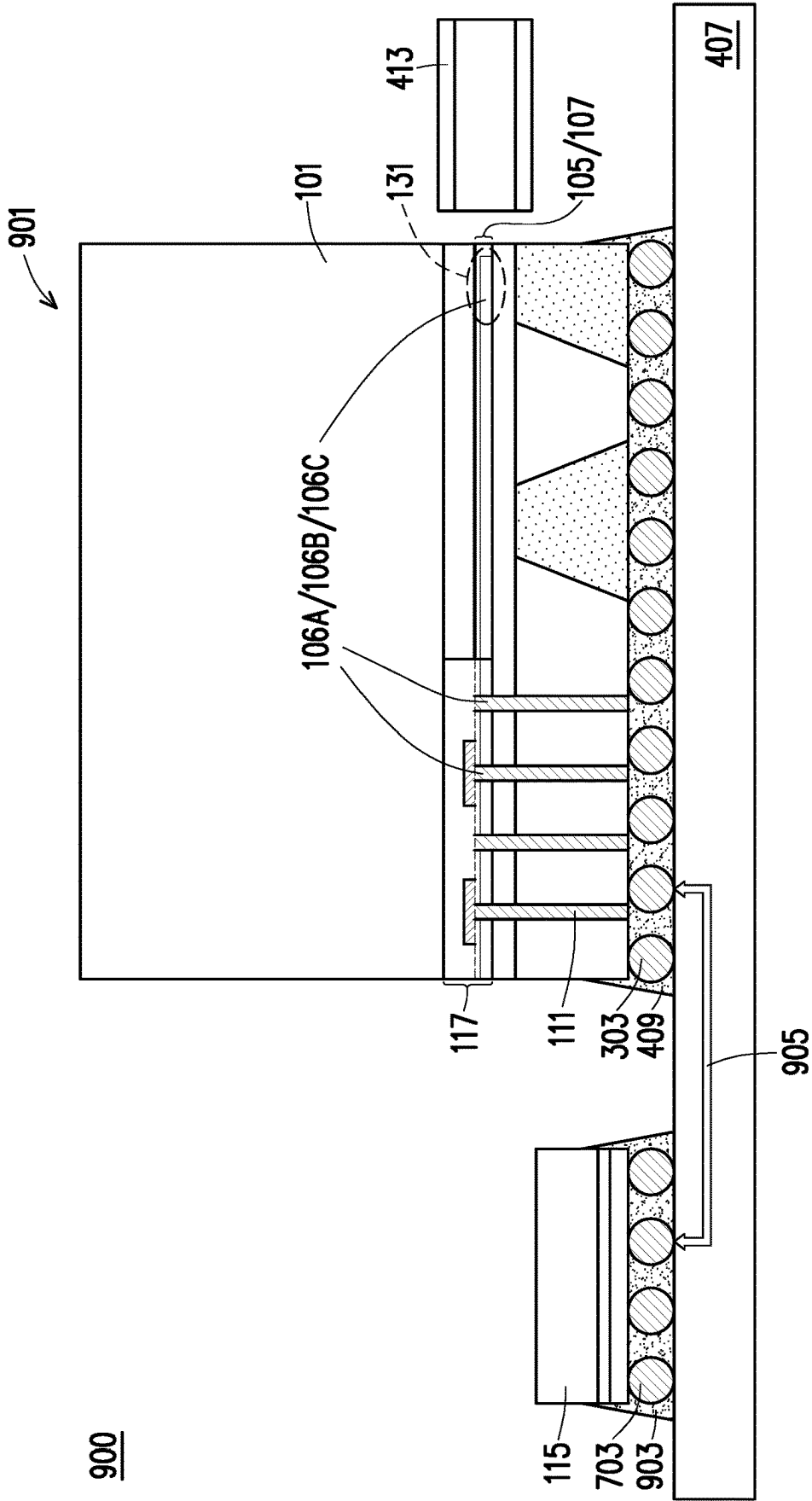


FIG. 9

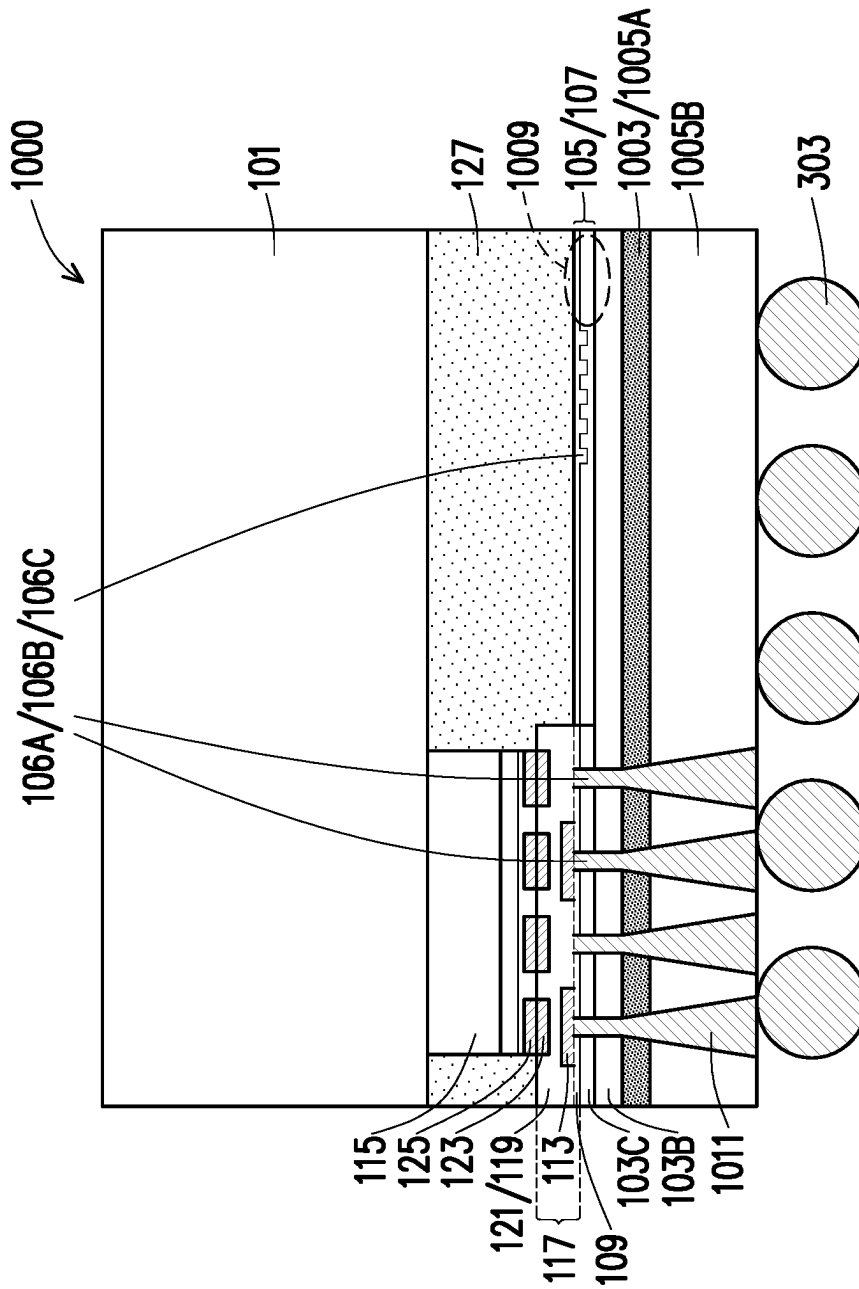


FIG. 10

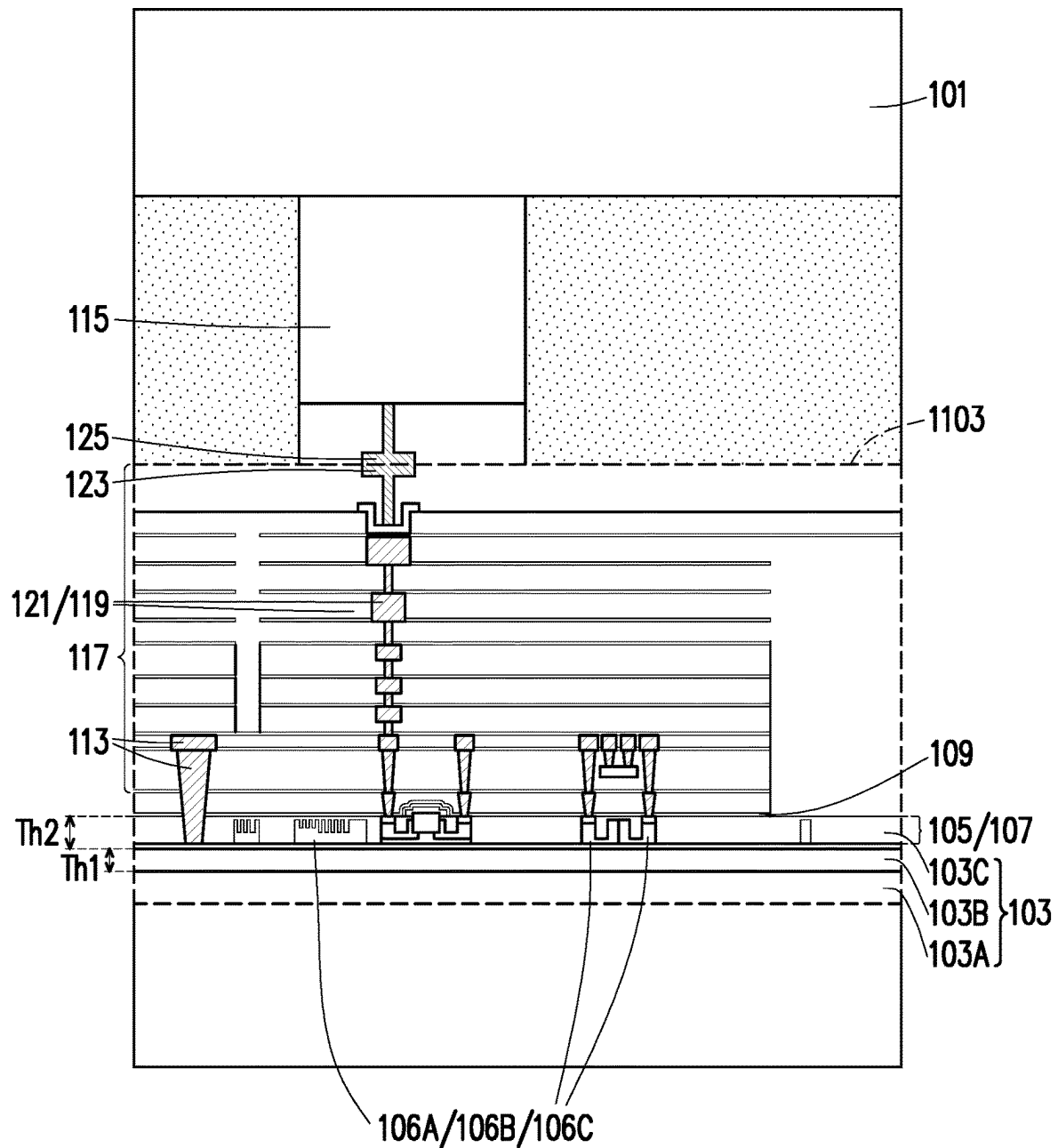


FIG. 11

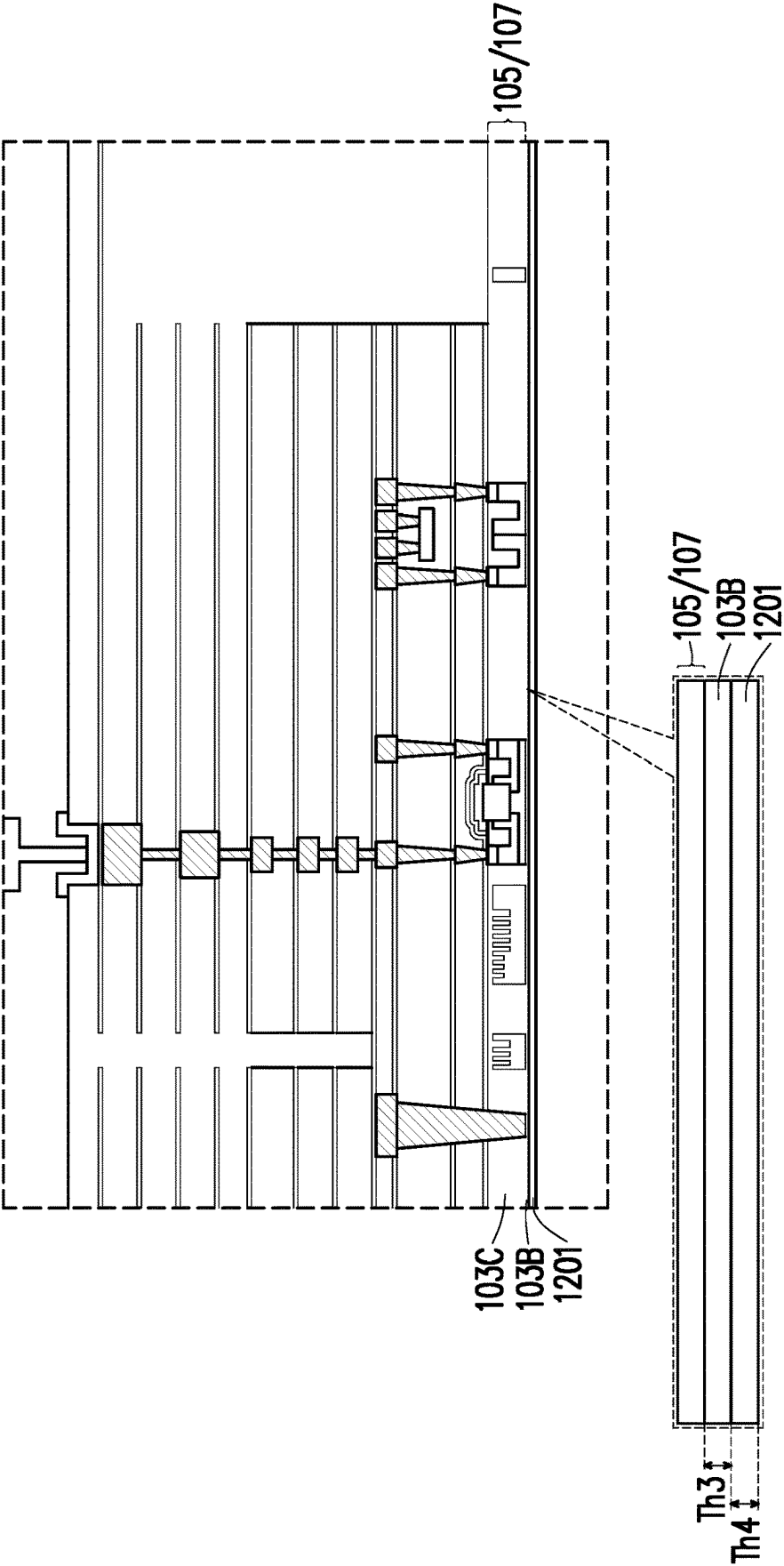


FIG. 12

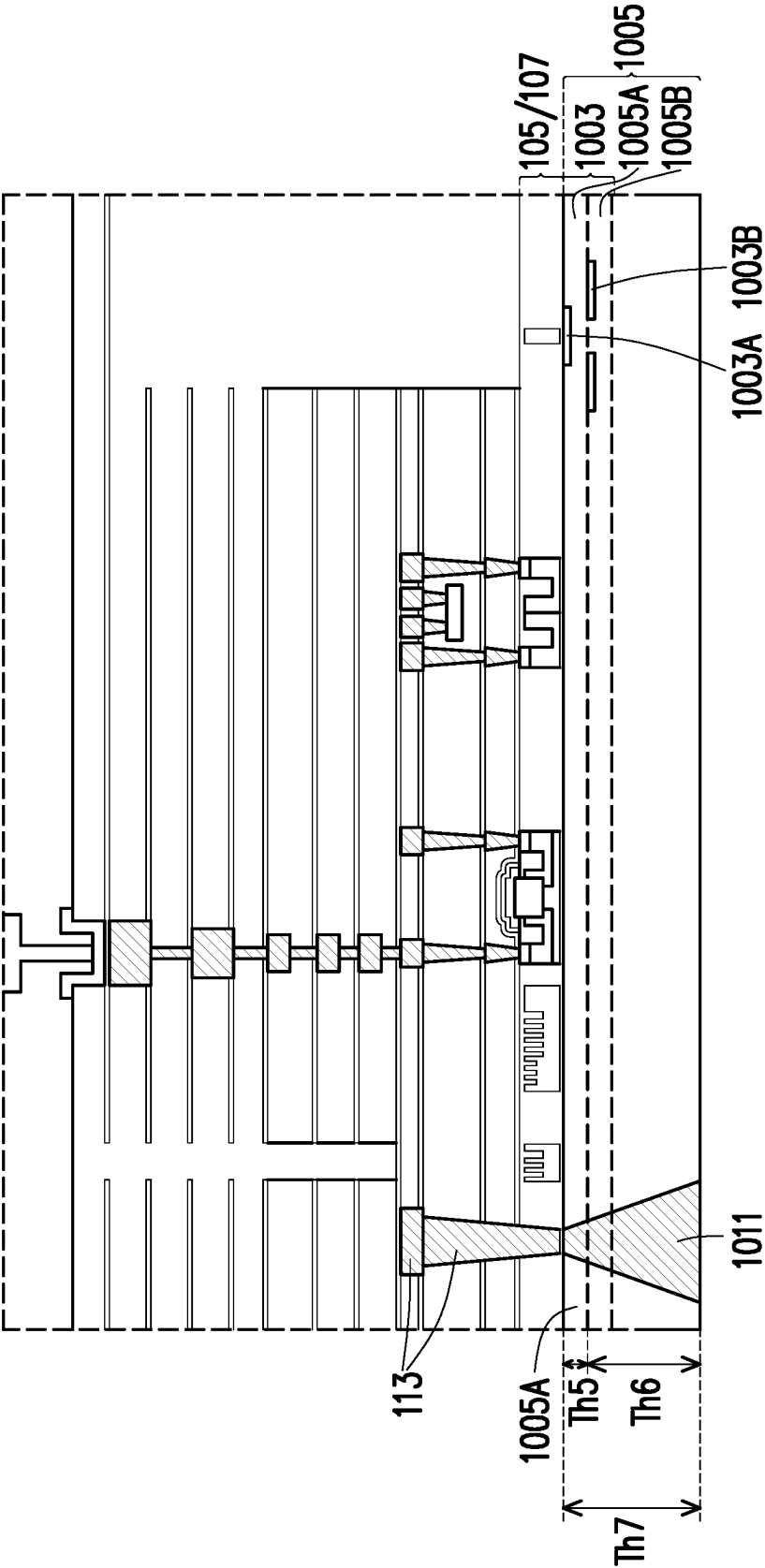


FIG. 13

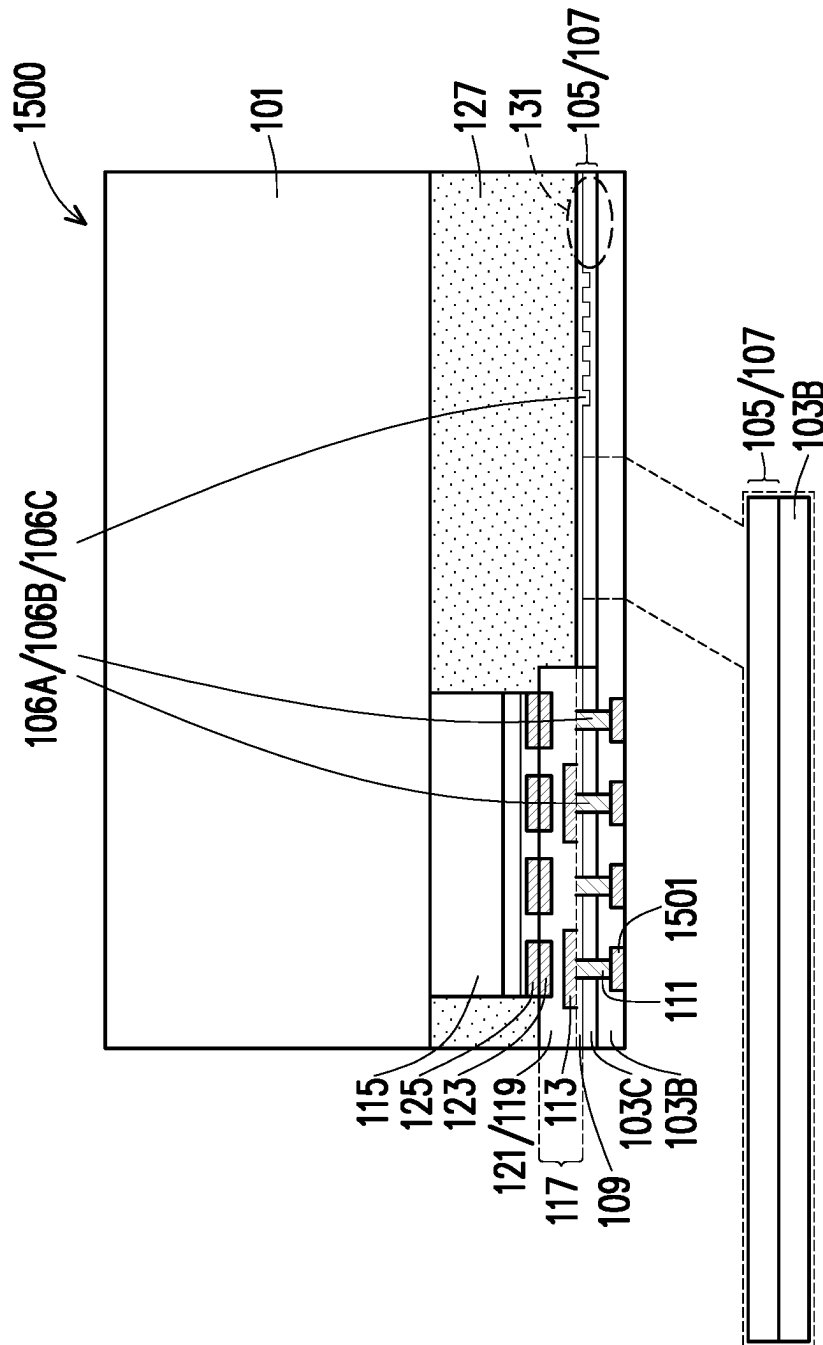


FIG. 15

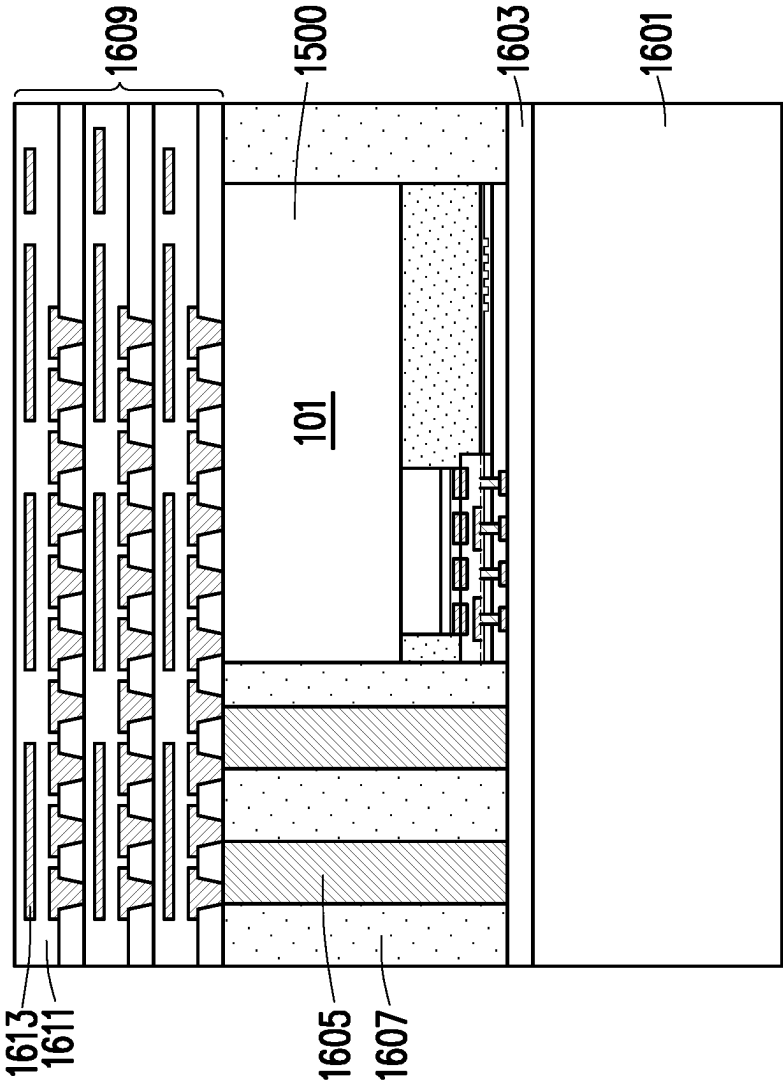


FIG. 16

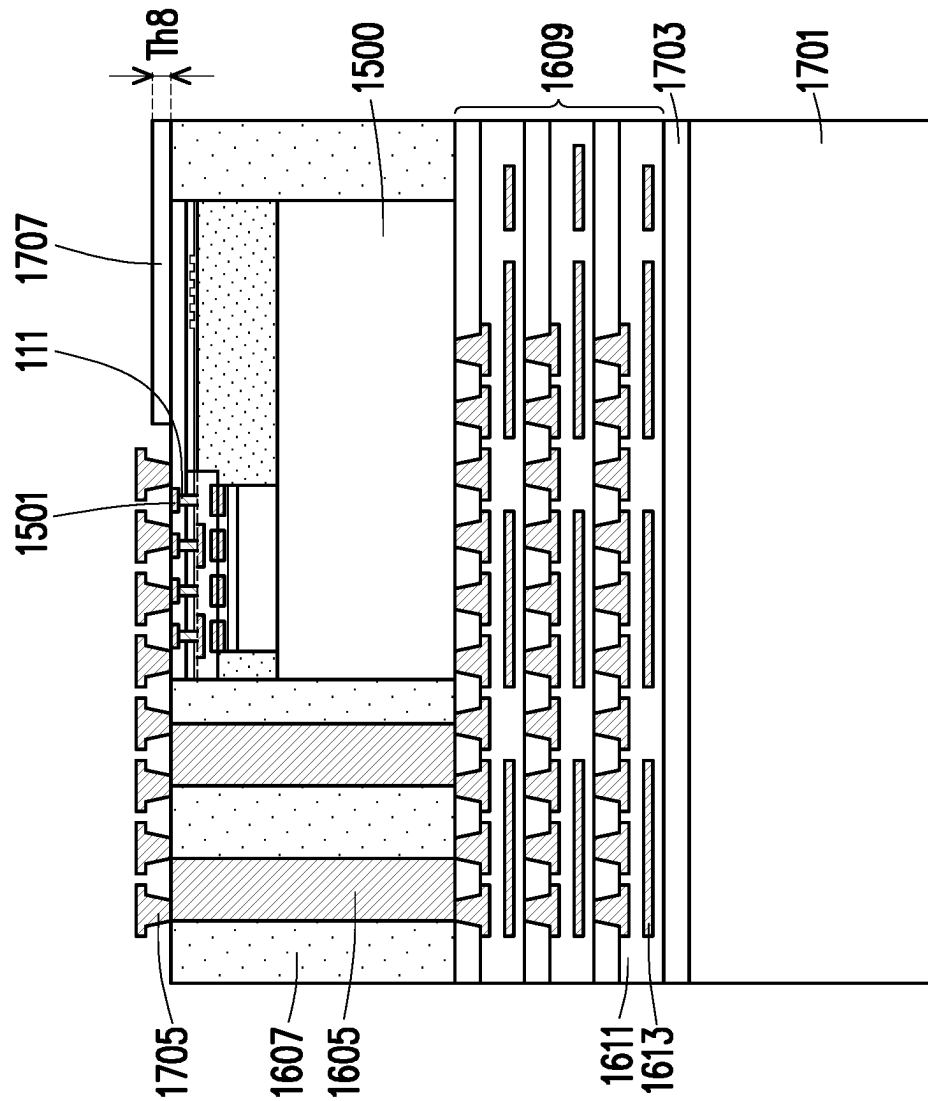


FIG. 17

1800

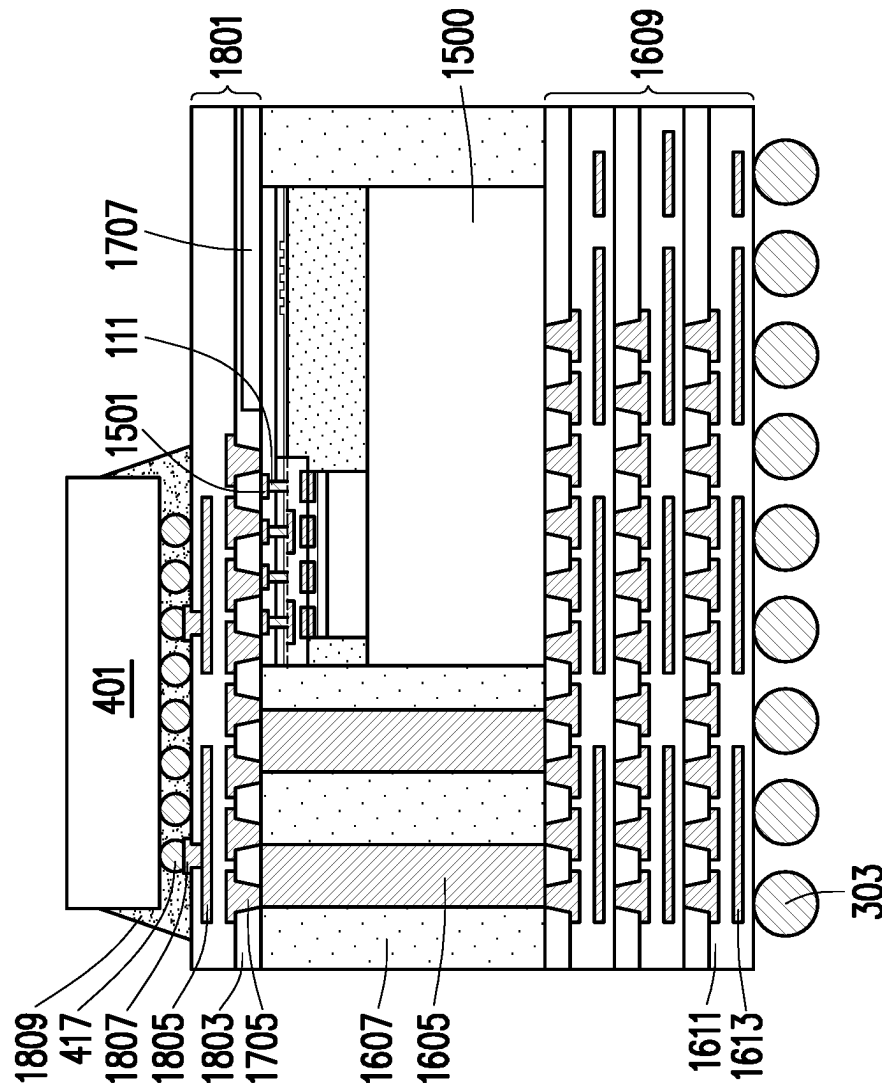


FIG. 18

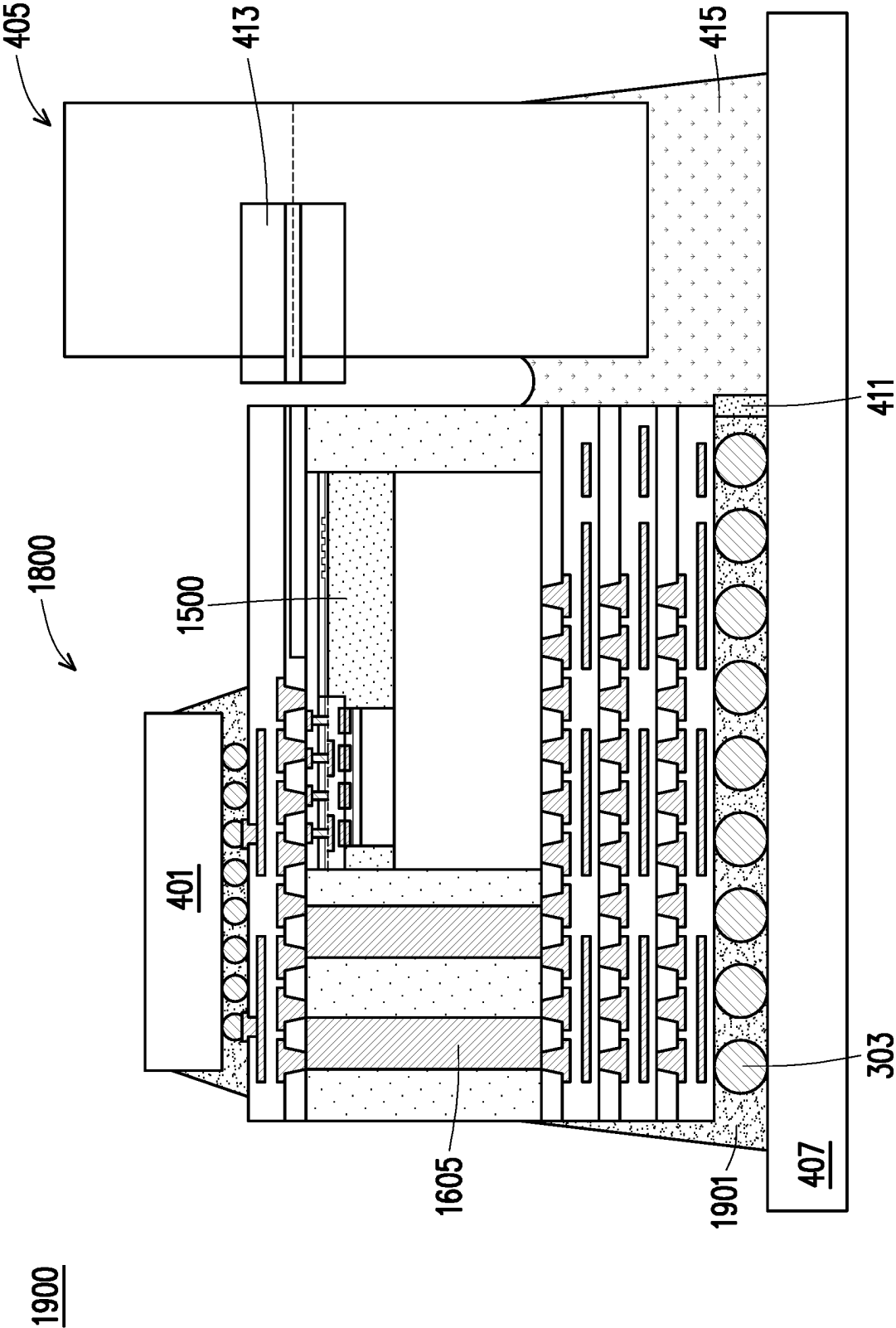


FIG. 19

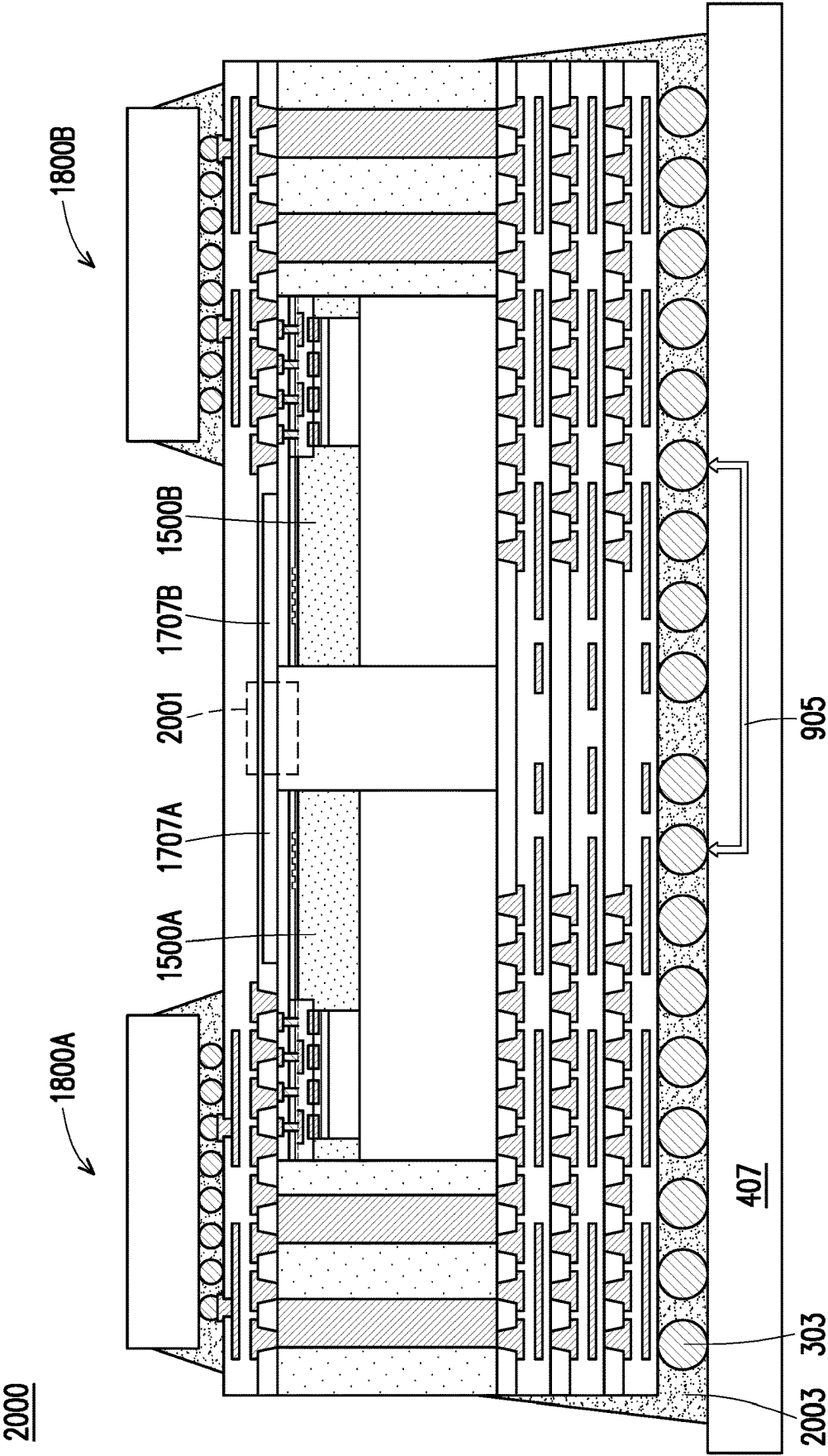


FIG. 20

2100

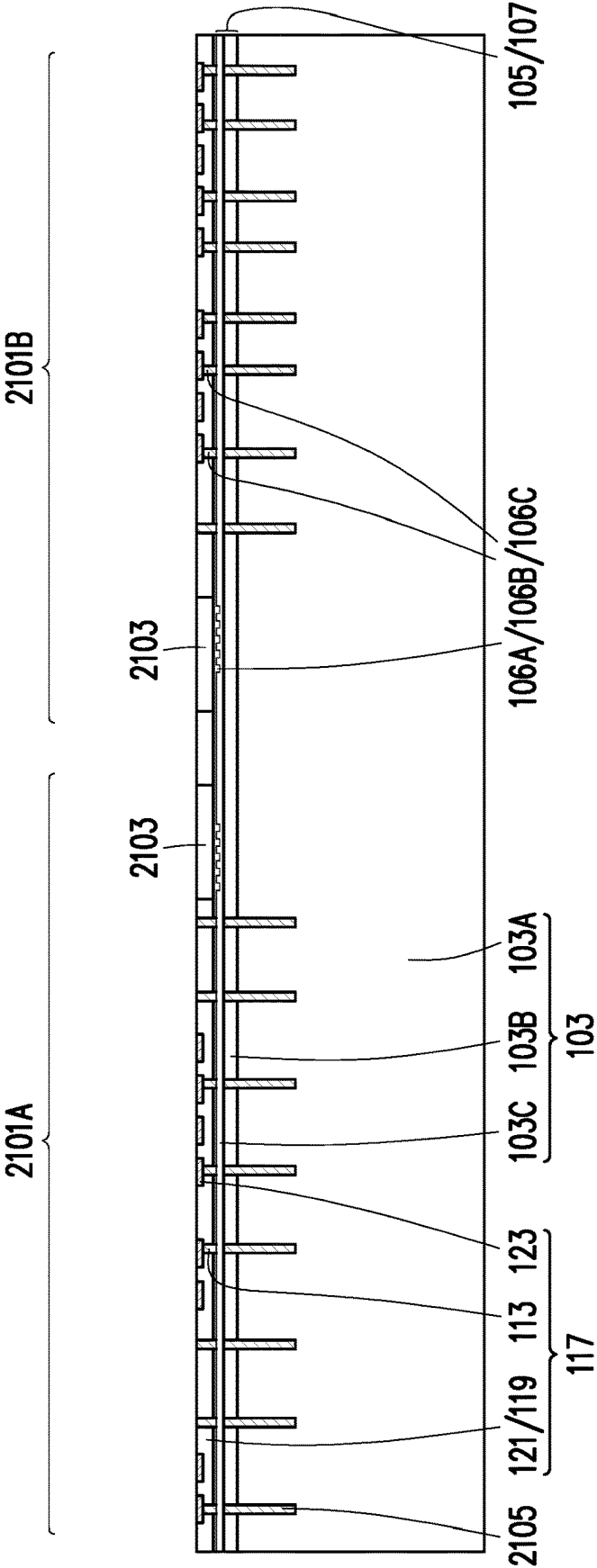


FIG. 21

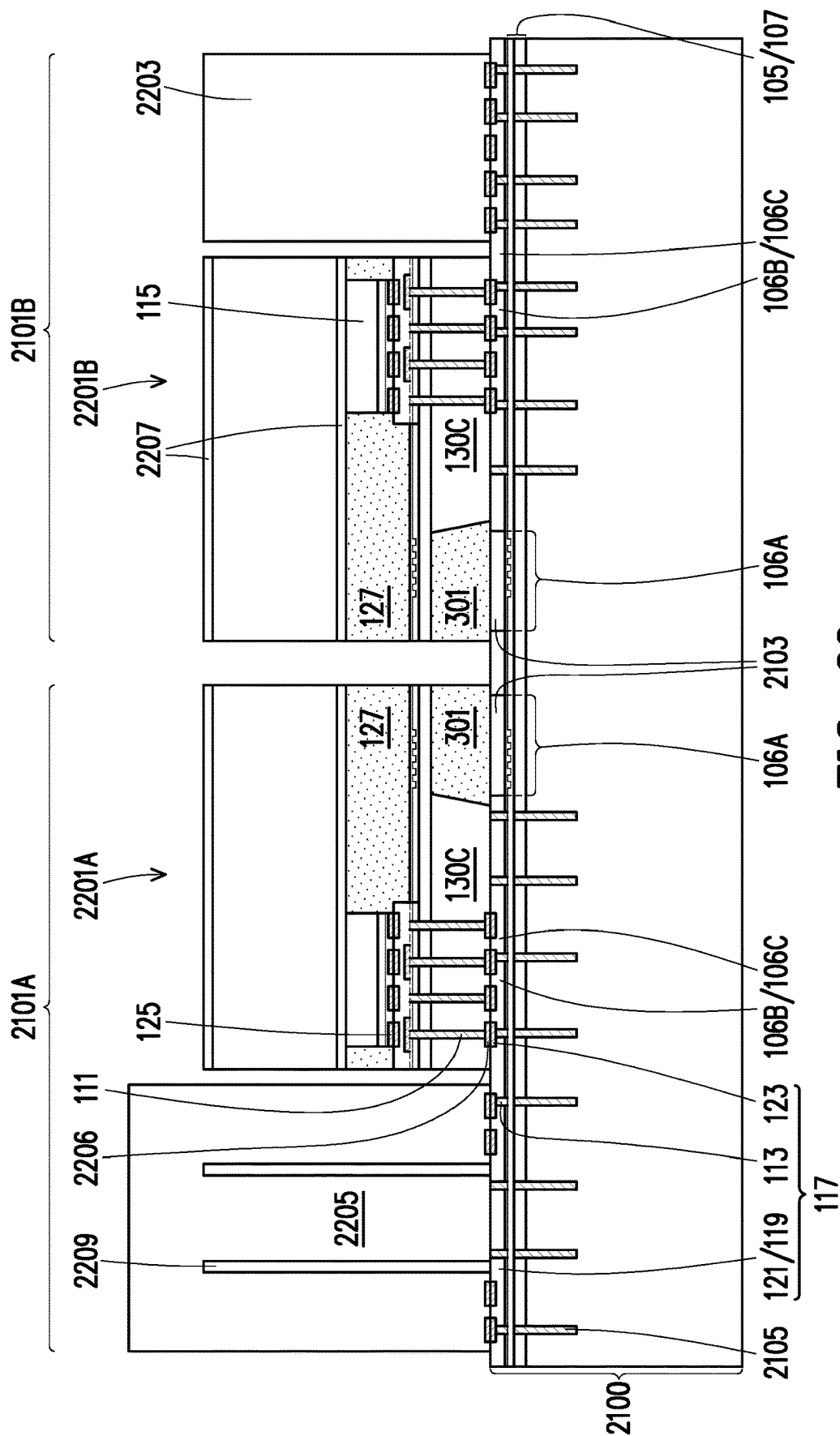


FIG. 22

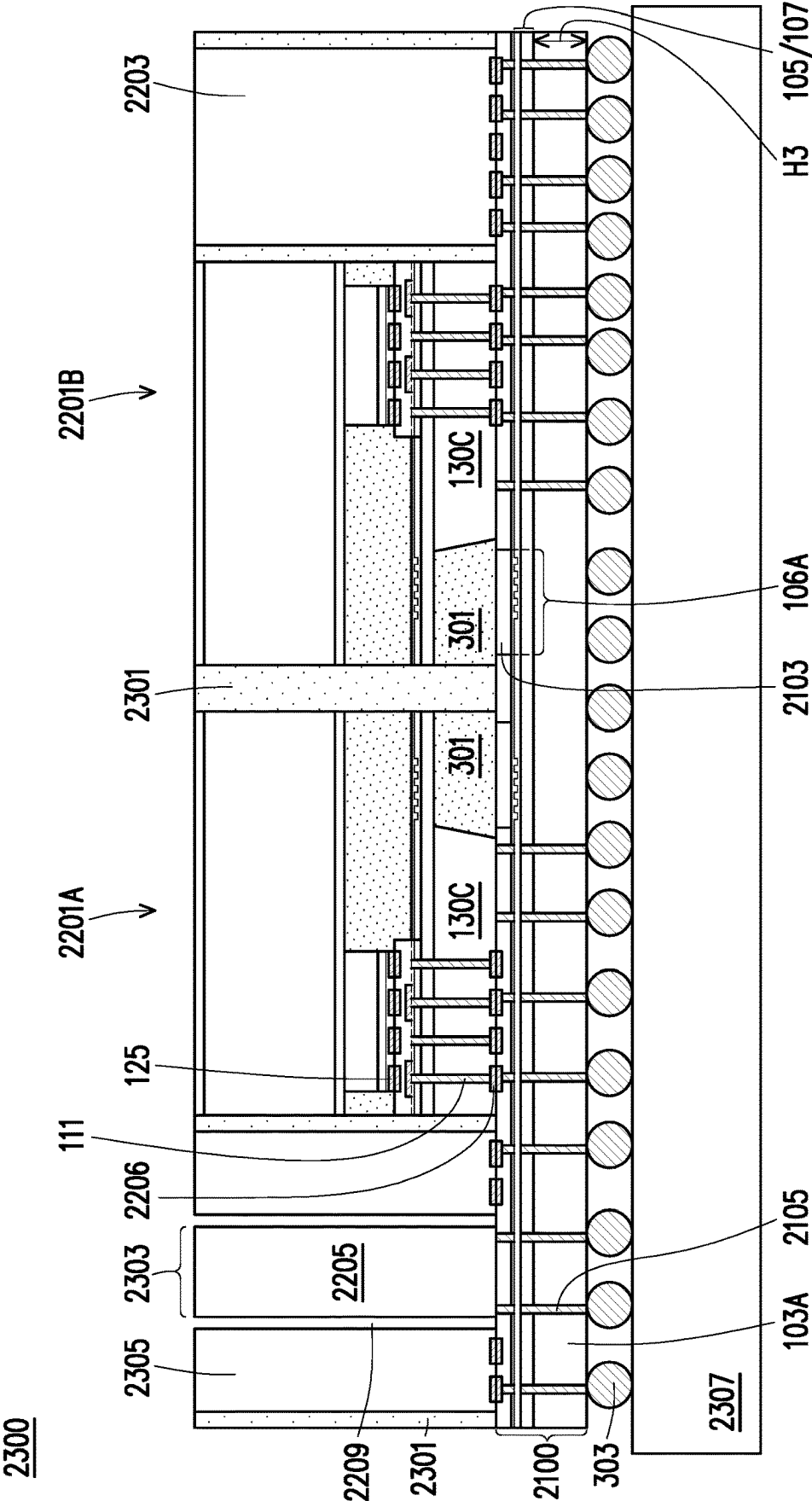


FIG. 23

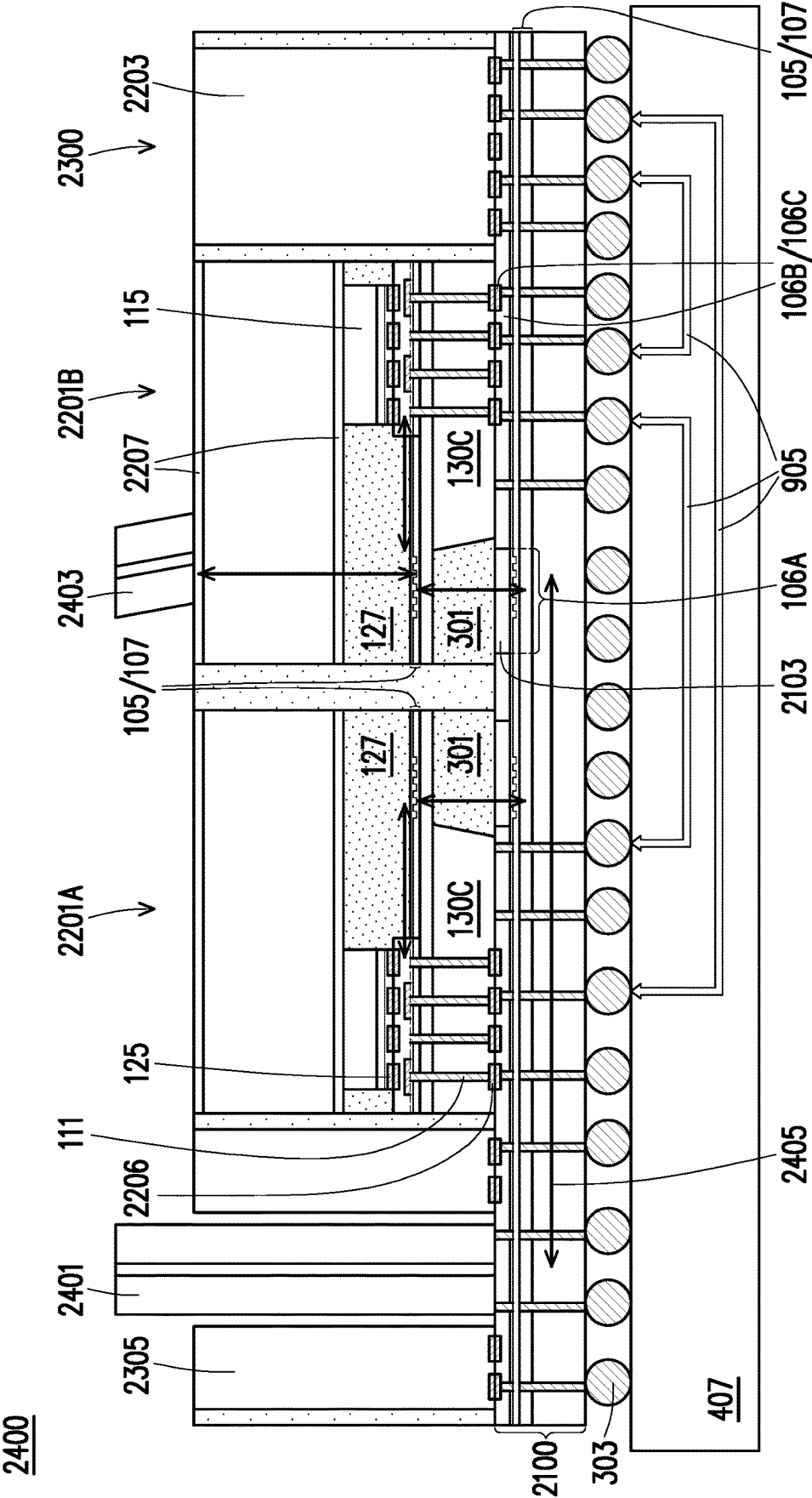


FIG. 24

2500

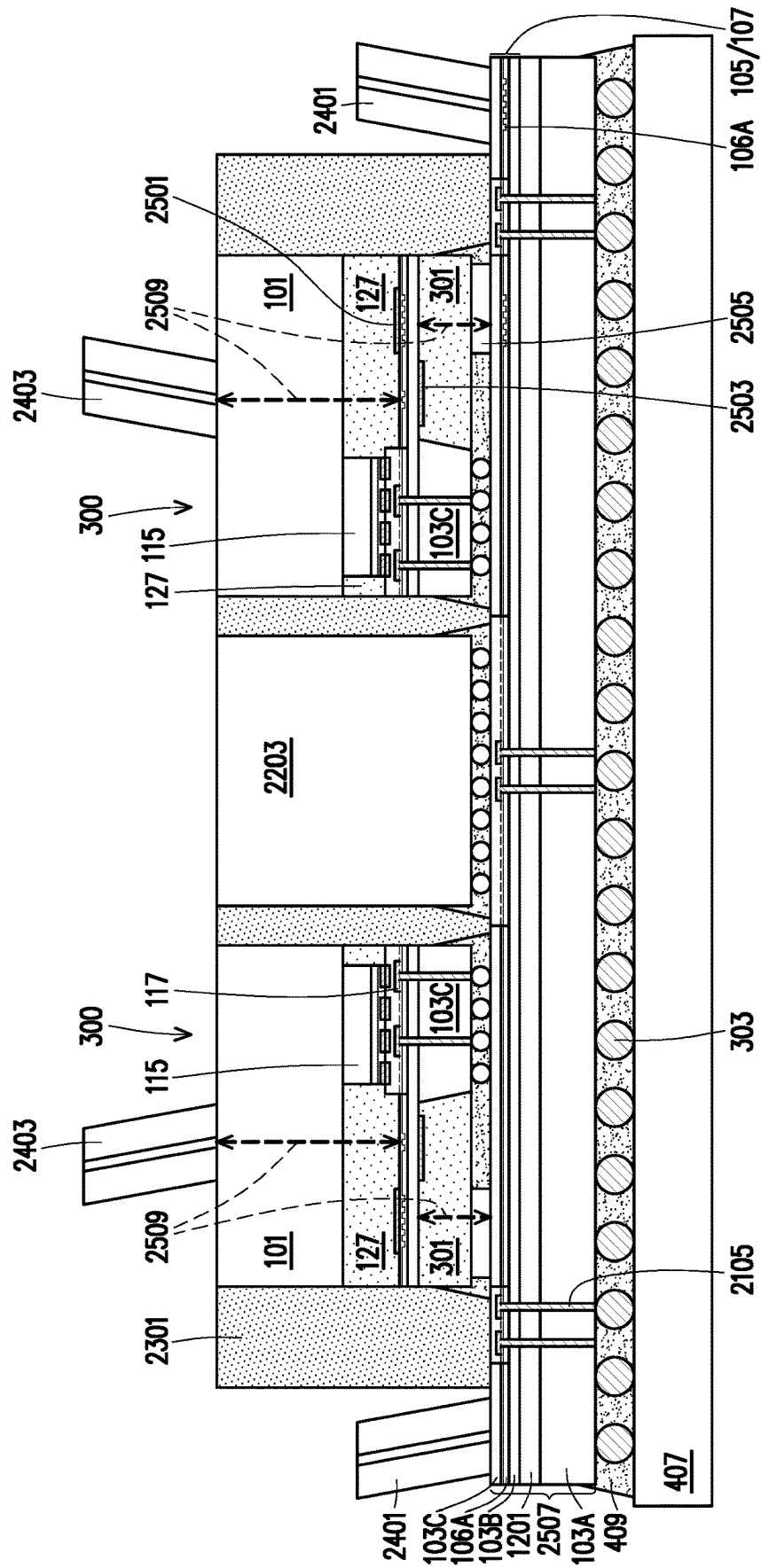


FIG. 25

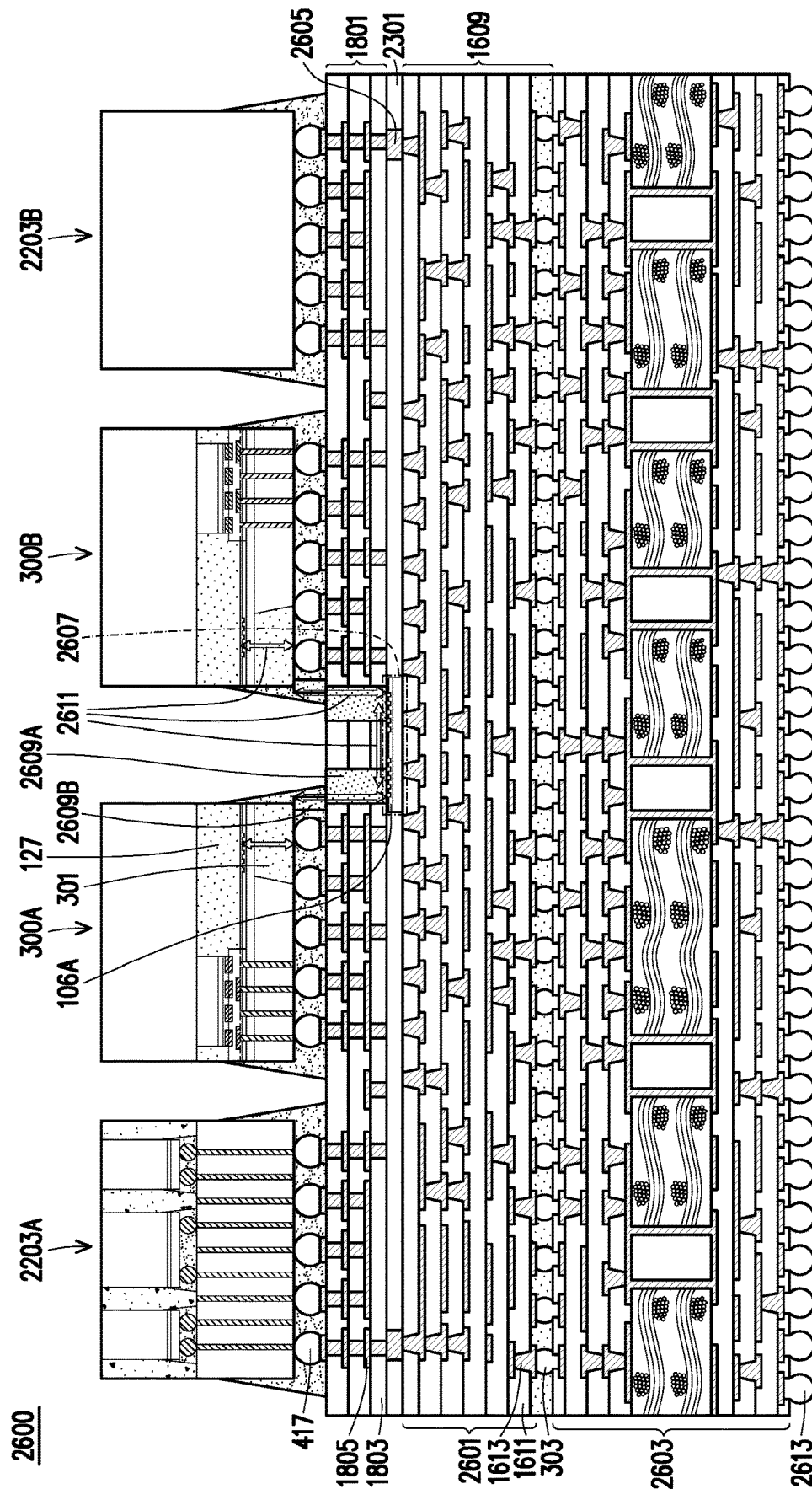


FIG. 26

STRUCTURE AND PROCESS FOR PHOTONIC PACKAGES

PRIORITY CLAIM AND CROSS-REFERENCE

This application is a divisional of U.S. patent application Ser. No. 17/232,567, filed on Apr. 16, 2021, now U.S. Pat. No. 12,135,454, issued Nov. 5, 2024, which application is hereby incorporated herein by reference.

BACKGROUND

Electrical signaling and processing have been the mainstream techniques for signal transmission and processing. Optical signaling and processing have been used in increasingly more applications in recent years, particularly due to the use of optical fiber-related applications for signal transmission.

Optical signaling and processing are typically combined with electrical signaling and processing to provide full-fledged applications. For example, optical fibers may be used for long-range signal transmission, and electrical signals may be used for short-range signal transmission as well as processing and controlling. Accordingly, devices integrating optical components and electrical components are formed for the conversion between optical signals and electrical signals, as well as the processing of optical signals and electrical signals. Packages thus may include both optical (photonic) dies including optical devices and electronic dies including electronic devices.

BRIEF DESCRIPTION OF THE DRAWINGS

Aspects of the present disclosure are best understood from the following detailed description when read with the accompanying figures. It is noted that, in accordance with the standard practice in the industry, various features are not drawn to scale. In fact, the dimensions of the various features may be arbitrarily increased or reduced for clarity of discussion.

FIGS. 1A, 1B, 2, and 3 illustrate cross-sectional views of forming a first optical engine, in accordance with some embodiments.

FIG. 4 illustrates a first package assembly using the first optical engine, according to some embodiments.

FIG. 5 illustrates formation of an optional groove feature in the first optical engine for passive alignment with a fiber attachment unit, according to some embodiments.

FIGS. 6-8 illustrate formation of a second optical engine and second package assembly, according to some embodiments.

FIG. 9 illustrates a third package assembly using a third optical engine, according to some embodiments.

FIGS. 10-13 illustrate formation of a fourth optical engine, according to yet some further embodiments.

FIG. 14 illustrates formation of a fourth package assembly using the fourth optical engine, according to some embodiments.

FIGS. 15-18 illustrate formation of a fifth optical engine, according to still further embodiments.

FIG. 19 illustrates a fifth package assembly using the fifth optical engine, according to some further embodiments.

FIG. 20 illustrates a sixth package assembly using two optical engines, according to some further embodiments.

FIGS. 21-24 illustrate formation of a seventh package assembly using two optical engines, according to still further embodiments.

FIG. 25 illustrates formation of an eighth package assembly using two optical engines, according to still further embodiments.

FIG. 26 illustrates formation of a ninth package assembly using two optical engines, according to still further embodiments.

DETAILED DESCRIPTION

The following disclosure provides many different embodiments, or examples, for implementing different features of the invention. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. For example, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed between the first and second features, such that the first and second features may not be in direct contact. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed.

Further, spatially relative terms, such as “beneath,” “below,” “lower,” “above,” “upper” and the like, may be used herein for ease of description to describe one element or feature’s relationship to another element(s) or feature(s) as illustrated in the figures. The spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. The apparatus may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein may likewise be interpreted accordingly.

Embodiments will now be described with respect to specific methods and processes which work to protect sensitive components of photonic integrated circuits such as grating couplers and waveguides and packages formed using the photonic integrated circuits. However, the embodiments discussed herein are intended to be representative and are not meant to limit the embodiments in any fashion. The intermediate stages of forming the packages are illustrated, in accordance with some embodiments. Some variations of some embodiments are discussed. Throughout the various views and illustrative embodiments, like reference numbers are used to designate like elements.

FIGS. 1A and 1B illustrate cross-sectional views of intermediate structures formed during intermediate steps in forming a first optical engine 300 (see FIG. 3), in accordance with some embodiments. FIG. 1B represents a magnified view of a first region 129 of the intermediate structure illustrated in FIG. 1A.

The first optical engine 300 may be formed by initially forming a buried oxide (“BOX”) substrate 103, in accordance with some embodiments. The BOX substrate 103 comprises an buried oxide layer 103B located over a semiconductor substrate 103A, and a silicon layer 103C located over the buried oxide layer 103B. The semiconductor substrate 103A may be, for example, a material such as a glass, ceramic, dielectric, a semiconductor, the like, or a combination thereof. In some embodiments, the semiconductor substrate 103A may be a semiconductor substrate, such as a bulk semiconductor or the like, which may be doped (e.g., with a p-type or an n-type dopant) or undoped. The semi-

conductor substrate **103A** may be a wafer, such as a silicon wafer (e.g., a 12 inch silicon wafer, or the like). Other substrates, such as a multi-layered or gradient substrate may also be used. In some embodiments, the semiconductor material of the semiconductor substrate **103A** may include silicon; germanium; a compound semiconductor including silicon carbide, gallium arsenic, gallium phosphide, indium phosphide, indium arsenide, and/or indium antimonide; an alloy semiconductor including SiGe, GaAsP, AlInAs, AlGaAs, GaInAs, GaInP, and/or GaInAsP; or combinations thereof. The buried oxide layer **103B** may be, for example, a silicon oxide or the like. In some embodiments, the buried oxide layer **103B** may have a first thickness Th1 of between about 0.5 μm and about 4 μm , in some embodiments. The silicon layer **103C** may be, for example, silicon, silicon nitride (SiN), or the like. In some embodiments, the silicon layer **103C** may have a second thickness Th2 of between about 0.1 μm and about 1.5 μm , in some embodiments. However, any suitable thicknesses may be used for the first thickness Th1 and the second thickness Th2. The BOX substrate **103** may be referred to as having a front side or front surface (e.g., the side facing upwards in FIG. 1A), and a back side or back surface (e.g., the side facing downwards in FIG. 1A).

In some embodiments first through insulator vias (TIVs) **111** may be formed by initially forming via openings extending through one or more of the patterned silicon layer **103C**, the buried oxide layer **103B**, and into but not through the semiconductor substrate **103A**. The via openings may be formed by acceptable photolithography and etching techniques, such as by forming and patterning a photoresist and then performing an etching process using the patterned photoresist as an etching mask. Once the via openings have been formed, a conductive material is formed in the via openings, thereby forming the first TIVs **111**, in accordance with some embodiments. In some embodiments, a liner (not shown), such as a diffusion barrier layer, an adhesion layer, or the like, may be formed in the openings from TaN, Ta, TiN, Ti, CoW, or the like, and may be formed using suitable a deposition process such as ALD or the like. In some embodiments, a seed layer (not shown), which may include copper or a copper alloy may then be deposited in the via openings. The conductive material of the first TIVs **111** is formed in the via openings using, for example, electrochemical plating (ECP) or electro-less plating. The conductive material may include, for example, a metal or a metal alloy such as copper, silver, gold, tungsten, cobalt, aluminum, or alloys thereof. A planarization process, such as a CMP process or mechanical grinding may be performed to remove excess conductive material and planarize the first TIVs **111** with the chosen layer (e.g., the buried oxide layer **103B** as illustrated, although any suitable layer may be chosen).

According to some embodiments, the silicon layer **103C** is patterned to form first waveguides **105** and/or first photonic components **107**, in accordance with some embodiments. The silicon layer **103C** may be patterned using suitable photolithography and etching techniques. For example, a hardmask layer (e.g., a nitride layer or other dielectric material, not shown in FIG. 1A) may be formed over the silicon layer **103C** and patterned, in some embodiments. The pattern of the hardmask layer may then be transferred to the silicon layer **103C** using one or more etching techniques, such as dry etching and/or wet etching techniques. For example, the silicon layer **103C** may be etched to form recesses, the remaining un-recessed portions of the silicon layer **103C** forming one or more of the first

waveguides **105**. In the case of a plurality of the first waveguides **105** being formed, the first waveguides **105** may be individual separate waveguides or connected as a single continuous structure (e.g., continuous loop). The patterned silicon layer **103C** may also be referred to herein as a “photonic layer.”

The first photonic components **107** may be integrated with the first waveguides **105**, and contacts may be formed over the first photonic components **107**. The first photonic components **107** may be optically coupled to the first waveguides **105** to interact with optical signals within the first waveguides **105**. The first photonic components **107** may include, for example, grating couplers, photodetectors, and/or modulators. For example, a grating coupler **106A** may be optically coupled to a first waveguide **105** to externally transmit the optical signal within the first waveguide **105** (e.g., to an optical fiber **413**, see FIG. 4), a photodetector **106B** may be optically coupled to a first waveguide **105** to detect optical signals within the first waveguide **105**, and a modulator **106C** may be optically coupled to a first waveguide **105** to generate optical signals within the first waveguide **105** by modulating optical power within the first waveguide **105**. In this manner, the first photonic components **107** facilitate the input/output (I/O) of optical signals to and from the first waveguides **105**. In other embodiments, the first photonic components **107** may include other active or passive components, such as laser diodes, waveguide edge couplers, optical signal splitters, or other types of photonic structures or devices. Optical power may be provided to the first waveguides **105** by, for example, the optical fiber **413** (see FIG. 4) or generated by a first photonic component **107** such as a laser diode.

The grating couplers **106A** may be formed using acceptable photolithography and etching techniques. In an embodiment, the grating couplers **106A** are formed after the first waveguides **105** are defined. For example, a photoresist may be formed on the first waveguides **105** and patterned. The photoresist may be patterned with openings corresponding to the grating couplers **106A**. One or more etching processes may be performed using the patterned photoresist as an etching mask to form recesses in the first waveguides **105** that define the grating couplers **106A**. The etching processes may include one or more dry etching processes and/or wet etching processes.

In some embodiments, the photodetectors **106B** may be formed by, for example, etching regions of the first waveguides **105** and growing an epitaxial material on the remaining silicon of the etched regions. The first waveguides **105** may be etched using acceptable photolithography and etching techniques. The epitaxial material may be, for example a semiconductor material such as germanium (Ge), which may be doped or un-doped. In some embodiments, an implantation process may be performed to introduce dopants within the silicon of the etched regions as part of the formation of the photodetector **106B**. The silicon of the etched regions may be doped with p-type dopants, n-type dopants, or a combination.

In some embodiments, the modulators **106C** may be formed by, for example, etching regions of the first waveguides **105** and then implanting appropriate dopants within the remaining silicon of the etched regions. The first waveguides **105** may be etched using acceptable photolithography and etching techniques. In some embodiments, the etched regions used for the photodetectors **106B** and the etched regions used for the modulators **106C** may be formed using one or more of the same photolithography or etching steps. The silicon of the etched regions may be doped with

p-type dopants, n-type dopants, or a combination. In some embodiments, the etched regions used for the photodetectors **106B** and the etched regions used for the modulators **106C** may be implanted using one or more of the same implantation steps.

In accordance with some embodiments, a passivation layer **109** is formed on the front side of the BOX substrate **103**. The passivation layer **109** is formed over the first waveguides **105** and the first photonic components **107** patterned into the silicon layer **103C** and over the buried oxide layer **103B**. The passivation layer **109** may be formed of silicon oxide, silicon nitride, a combination thereof, or the like, and may be formed by CVD, PVD, atomic layer deposition (ALD), a spin-on-dielectric process, the like, or a combination thereof. In some embodiments, the passivation layer **109** may be formed by a high density plasma chemical vapor deposition (HDP-CVD), a flowable CVD (FCVD) (e.g., a CVD-based material deposition in a remote plasma system and post curing to make it convert to another material, such as an oxide), the like, or a combination thereof. Other dielectric materials formed by any acceptable process may be used. In some embodiments, the passivation layer **109** is then planarized using a planarization process such as a chemical-mechanical polishing (CMP) process, a grinding process, or the like.

Due to the difference in refractive indices of the materials of the first waveguides **105** and passivation layer **109**, the first waveguides **105** have high internal reflections such that light is confined within the first waveguides **105**, depending on the wavelength of the light and the reflective indices of the respective materials. In an embodiment, the refractive index of the material of the first waveguides **105** is higher than the refractive index of the material of the passivation layer **109**.

FIGS. 1A and 1B also show the formation of a series of conductive feature **121**, dielectric layers **119**, and contacts **113** that extend to the first TIVs **111** and the first photonic components **107** as part of a photonic die **117**. In an embodiment the photonic die **117** comprises the dielectric layers **119** and contacts **113** and conductive feature **121** formed in the dielectric layers **119** that provide interconnections and optical/electrical routing between the electronic die **115** and the first waveguide **105** and the first photonic components **107**. For example, the photonic die **117** may electrically connect the first TIVs **111**, the contacts **113** of the first photonic components **107**, and overlying devices such as electronic die **115**. The dielectric layers **119** may be, for example, insulating or passivating layers, and may include a material similar to those described above for the passivation layer **109**, such as a silicon oxide, or may include a different material. The dielectric layers **119** may be formed using a technique similar to those described above for the passivation layer **109** or using a different technique. The conductive feature **121** may include conductive lines and vias, and may be formed by a damascene process, e.g., dual damascene, single damascene, or the like. In the topmost layer of the photonic die **117**, conductive pads **123** are formed in the dielectric layers **119**. A planarization process (e.g., a CMP process or the like) may be performed after forming the conductive pads **123** such that surfaces of the conductive pads **123** and the topmost dielectric layer **119** are substantially coplanar. The photonic die **117** may include more or fewer dielectric layers **119**, conductive feature **121**, or conductive pads **123** than shown in FIG. 1. The photonic die **117** may be formed having a thickness between about 4 μm and about 7 μm , in some embodiments. The photonic die **117** may also be referred to herein as a P-die or P-die layer.

For example, the contacts **113** may make electrical connection to the first photonic components **107** such as photodetectors **106B** and/or modulators **106C**. The contacts **113** allow electrical power or electrical signals to be transmitted to the first photonic components **107** and electrical signals to be transmitted from the first photonic components **107**. In this manner, the first photonic components **107** may convert electrical signals from an electronic die **115** into optical signals transmitted by the first waveguides **105**, and/or convert optical signals from the first waveguides **105** into electrical signals that may be received by the electronic die **115**. The contacts **113** may be formed before or after formation of the first TIVs **111**, and the formation of the contacts **113** and the formation of the first TIVs **111** may share some steps such as deposition of the conductive material or planarization. In some embodiments, the contact may be formed by a damascene process, e.g., dual damascene, single damascene, or the like. For example, in some embodiments, openings (not shown) for the contacts **113** are first formed in the passivation layer **109** using acceptable photolithography and etching techniques. A conductive material may then be formed in the openings, forming the contacts **113**. The conductive material of the contacts **113** may be formed of a metal or a metal alloy including aluminum, copper, tungsten, or the like, which may be the same as that of the first TIVs **111**. The contacts **113** may be formed using other techniques or materials in other embodiments.

According to some embodiments, the dielectric layers **119** are etched to expose a portion of the first waveguide **105**. The dielectric layers **119** may be etched using acceptable photolithography and etching techniques. The etch process may be any suitable process used to remove the material of the dielectric layers **119** without substantially removing material of the first waveguide **105**. Once the portion has been exposed, a first portion of a gap-fill material **127** may be used to fill and/or overfill the first portion of the first waveguide. The gap-fill material **127** may be formed of silicon oxide, silicon nitride, a polymer, the like, or a combination thereof. The gap-fill material **127** may be formed by CVD, PVD, ALD, a spin-on-dielectric process, the like, or a combination thereof. In some embodiments, the gap-fill material **127** may be formed by HDP-CVD, FCVD, the like, or a combination thereof. However, other dielectric materials formed by any acceptable process may be used.

Once deposited, the gap-fill material **127** may be planarized, in accordance with some embodiments. The gap-fill material **127** may be planarized using a planarization process such as a CMP process, a grinding process, or the like. The planarization process may expose the photonic die **117** such that surfaces of the photonic die **117** and surfaces of the gap-fill material **127** are coplanar.

Once the photonic die **117** has been formed, the electronic dies **115** are bonded to the photonic die **117**, in accordance with some embodiments. The electronic dies **115** may be, for example, semiconductor devices, dies, or chips that communicate with the first photonic components **107** using electrical signals. In some cases, a single electronic die **115** is incorporated into the first optical engine **300** (shown in FIG. 3). However, more than one electronic die **115** may be incorporated into the first optical engine **300** in order to reduce processing cost and/or based on the device design. The electronic dies **115** each include die connectors **125**, which may be, for example, conductive pads, conductive pillars, or the like. In some embodiments, the electronic dies **115** may have a thickness between about 10 μm and about 35 μm .

The electronic dies **115** may include integrated circuits for interfacing with the first photonic components **107**, such as circuits for controlling the operation of the first photonic components **107**. The electronic die **115** may also include a CPU, in some embodiments. In some embodiments, the electronic dies **115** include circuits for processing electrical signals received from first photonic components **107**, such as electrical signals received from the photodetector **106B**. The electronic dies **115** may include controllers, drivers, transimpedance amplifiers, the like, or combinations thereof. The electronic dies **115** may control high-frequency signaling of the first photonic components **107** according to electrical signals (digital or analog) received from another device, such as from a computing package (e.g., application specific integrated circuit **401** see FIG. **4**), in some embodiments. In some embodiments, the electronic dies **115** may be electronic integrated circuits (EICs) or the like that provide Serializer/Deserializer (SerDes) functionality. However, any suitable functionality may be utilized.

In some embodiments, the electronic dies **115** are bonded to the photonic die **117** by hybrid bonding. In such embodiments, covalent bonds are formed between oxide layers, such as the topmost layer of the dielectric layers **119** and surface dielectric layers (not shown) of the electronic dies **115**. During the hybrid bonding, metal bonding also occurs between the die connectors **125** of the electronic dies **115** and the conductive pads **123** of the photonic die **117**. By bonding the electronic dies **115** to the interconnect structure using hybrid bonding, the thickness of the resulting first optical engine **300** may be reduced, which may allow for improved electrical signal paths between the electronic dies **115**, the photonic die **117**, and the first photonic components **107**. This arrangement may also provide for improved optical coupling between grating couplers **106A** and optical fibers **413** (see FIG. **4**). Additionally, the use of hybrid bonding may allow for materials transparent to the relevant wavelengths of light (e.g., silicon oxide) to be used instead of opaque materials such as an encapsulant or a molding compound. This allows the photonic die **117** and electronic dies **115** to be located above the grating couplers **106A** and any other ones of the first photonic components **107** to be formed as described here. In this manner, the size or processing costs of a photonic structure may be reduced, and the optical coupling to external components may be improved.

In some embodiments, before performing the hybrid bonding process, a surface treatment is performed on the electronic dies **115**. In some embodiments, the top surfaces of the photonic die **117** and/or the electronic dies **115** may first be activated utilizing, for example, a dry treatment, a wet treatment, a plasma treatment, exposure to an inert gas, exposure to H₂, exposure to N₂, exposure to O₂, the like, or combinations thereof. However, any suitable activation process may be utilized. After the activation process, the photonic die **117** and/or the electronic dies **115** may be cleaned using, e.g., a chemical rinse. The electronic dies **115** are then aligned with the photonic die **117** and placed into physical contact with the photonic die **117**. The electronic dies **115** may be placed on the photonic die **117** using a pick-and-place process, for example. The photonic die **117** and the electronic dies **115** may then be subjected to a thermal treatment and/or pressed against each other (e.g., applying contact pressure) to hybrid bond the photonic die **117** and the electronic dies **115**. For example, photonic die **117** and the electronic dies **115** may be subjected to a pressure of about 200 kPa or less, and a temperature between about 200° C. and about 400° C. The photonic die **117** and

the electronic dies **115** may then be subjected to a temperature at or above the eutectic point of the material of the conductive pads **123** and the die connectors **125**, e.g., between about 150° C. and about 650° C. to fuse the conductive pads **123** and the die connectors **125**. In this manner, bonding of photonic die **117** and the electronic dies **115** forms a hybrid bonded structure. In some embodiments, the hybrid bonded structure is baked, annealed, pressed, or otherwise treated to strengthen or finalize the bond.

In other embodiments, the electronic dies **115** may be bonded to the photonic die **117** by direct surface bonding, metal-to-metal bonding, or another bonding process. A direct surface bonding process creates an oxide-to-oxide bond or substrate-to-substrate bond through a cleaning and/or surface activation process followed by applying pressure, heat and/or other bonding process steps to the joined surfaces. In some embodiments, the electronic dies **115** and the photonic die **117** are bonded by metal-to-metal bonding that is achieved by fusing conductive elements. Any suitable bonding process may be utilized.

Once the electronic die **115** is bonded to the photonic die **117**, a second portion of the gap-fill material **127** is formed over the electronic dies **115**, in accordance with some embodiments. Once deposited, the gap-fill material **127** may be planarized, in accordance with some embodiments. The planarization process may expose the electronic dies **115** such that surfaces of the electronic dies **115** and surfaces of the gap-fill material **127** are coplanar. After planarization, the gap-fill material **127** may have a thickness over the photonic die **117** that is between about 10 μm and about 40 μm, and may have a thickness over the waveguides **105** of about 20 μm. In some embodiments, the combined thickness of the passivation layer **109**, the dielectric layers **119**, and the gap-fill material **127** over the grating couplers **106A** may be between about 14 μm and about 50 μm. In some cases, a smaller combined thickness may allow for more efficient optical coupling. For example, in some embodiments, the combined thickness may be less than about 30 μm.

Once the gap-fill material **127** has been planarized, a support substrate **101** for mechanical strength may be attached to the coplanar surfaces of the electronic dies **115** and the gap-fill material **127** to provide support during further handling and processing. In an embodiment, the support substrate **101** may be attached using a fusion bonding process, such as an oxide-to-oxide fusion bonding process, or else through other processes, such as a die attach film.

a die attach film, such as an ultra-violet glue, which loses its adhesive properties when exposed to ultra-violet light. However, other types of adhesives, such as pressure sensitive adhesives, radiation curable adhesives, epoxies, combinations of these, or the like, may also be used. The adhesive may be placed onto the support substrate **101** in a semi-liquid or gel form, which is readily deformable under pressure. Once the support substrate **101** has been attached, the back side of the semiconductor substrate **103A** is thinned to expose the first TIVs **111**. The semiconductor substrate **103A** may be thinned by a CMP process, a mechanical grinding, or the like. According to some embodiments, the semiconductor substrate **103A** is thinned to a first height H1 that is less than about 25 μm, such as about 20 μm.

FIG. **2** illustrates a formation of a cavity **201** in the semiconductor substrate **103A**, according to some embodiments. Once the semiconductor substrate **103A** has been thinned, the cavity **201** may be formed through the semiconductor substrate **103A** using suitable photolithography and etching techniques (e.g., backside etch process).

According to some embodiments, the cavity **201** is formed at a location under the first waveguide **105** and exposes the buried oxide layer **103B**. In some embodiments, the cavity **201** may have angled sidewalls formed, for example, in a backside facet etch process. In other embodiments, the cavity **201** may have vertical sidewalls formed, for example, in an anisotropic etching process. In some embodiments, a portion of the exposed buried oxide layer **103B** may extend to a location of a sidewall of the resulting first optical engine **300** (shown in FIG. 3). However, any suitable location under the first waveguide **105** may be used.

FIG. 3 illustrates a formation of a first backfill structure **301** in the cavity **201** and formation of first external contacts **303** for the first optical engine **300**, according to some embodiments. The first backfill structure **301** may be formed within the cavity using any of the materials and techniques suitable for forming the gap-fill material **127**. In some embodiments, the first backfill structure **301** may be formed using a silicon oxide (SiO₂) material in a dielectric fill process (e.g., chemical vapor deposition). However, any suitable materials and processes may be used. In some embodiments, the first backfill structure **301** is deposited to fill and/or overfill the cavity **201**. Once deposited, the first backfill structure **301** is planarized with the coplanar surface of the semiconductor substrate **103A** and first TIVs **111** using a process such as chemical mechanical planarization. In other embodiments, the first backfill structure **301** may be formed using a molding material (e.g., molding compound, epoxy, or the like) in a molding process, such as, injection molding or the like. However, any suitable material and method may be utilized. The first backfill structure **301** may also be referred to herein as a first oxide substrate structure, an oxide substrate structure, a first oxide structure, or oxide structure.

By forming the first backfill structure **301** during the front end fabrication processes, materials more suitable for front end fabrication processes can be utilized. For example, the first backfill structure **301** may be formed with silicon oxide or other oxides instead of organic materials which are more associated with package fabrication processes. As such, the problems associated with package fabrication materials such as the organic materials, may be avoided.

Once the first backfill structure **301** has been formed (e.g., in the front end fabrication processes), first external contacts **303** are formed electrically coupled to the first TIVs **111** as external connection to the first optical engine **300**. In some embodiments, in these package fabrication processes, conductive pads may be formed on the first TIVs **111** exposed at the coplanar surface of the semiconductor substrate **103A**. The conductive pads may be, for example, aluminum pads or aluminum-copper pads, although other metallic pads also may be used. In some embodiments, a passivation film may be formed on the semiconductor substrate **103A**, covering the conductive pads. The passivation film may be formed from a dielectric material, such as silicon oxide, silicon nitride, the like, or combinations thereof. Openings may be formed through the passivation film to expose central portions of the conductive pads. A process such as electroplating may be used to form underbump metallizations (UBMs) to the conductive pads and over the passivation film, in some embodiments. The UBMs may be formed from copper, a copper alloy, silver, gold, aluminum, nickel, the like, or combinations thereof. Once the UBMs have been formed, the first external contacts **303** may be attached to the UBMs.

According to some embodiments, the first external contacts **303** may be controlled collapse chip connection (C4) bumps, ball grid array (BGA) connectors, solder balls, metal

pillars, micro bumps, electroless nickel-electroless palladium-immersion gold technique (ENEPIG) formed bumps, or the like. The first external contacts **303** may include a conductive material such as solder, copper, aluminum, gold, nickel, silver, palladium, tin, the like, or a combination thereof. In some embodiments, the first external contacts **303** are formed by initially forming a layer of solder through methods such as evaporation, electroplating, printing, solder transfer, ball placement, or the like. Once a layer of solder has been formed on the structure, a reflow may be performed in order to shape the material into the desired bump shapes. In another embodiment, the first external contacts **303** are metal pillars (such as a copper pillar) formed by a sputtering, printing, electro plating, electroless plating, CVD, or the like. The metal pillars may be solder free and have substantially vertical sidewalls. In some embodiments, a metal cap layer (not shown) is formed on the top of the first external contacts **303**. The metal cap layer may include nickel, tin, tin-lead, gold, silver, palladium, indium, nickel-palladium-gold, nickel-gold, the like, or a combination thereof and may be formed by a plating process.

Further, by packaging the first optical engine **300** using the backside etch process to form the cavity **201**, a dielectric fill process to form the first backfill structure **301**, and a planarization process (e.g., CMP) to planarize the first backfill structure **301**, this enables a robust structure and simpler manufacturing process for packaging the first optical engine **300**. Using oxide type materials to form the first optical engine **300** allows for much of the manufacturing process to be performed in front end of the line (FEOL) fabrication facilities. As such, greater processing control and improved optical integrity is maintained for the fabrication of the first optical engine **300**. Furthermore, the first optical engine **300** is modularized in a stand-alone package that can achieve good die to die bandwidths by reducing the pitches of the conductive feature **121**, the dielectric layers **119**, and the conductive pads **123** of the photonic die **117** and the first TIVs **111**. As such, the first optical engine **300** formed in the stand alone package can be quickly installed as desired with other packages or even co-packaged with other packages allowing for the first optical engine **300** to be used and incorporated in a wide variety of uses with a minimum or re-design.

FIG. 4 illustrates a first package assembly **400**, according to some embodiments. The first package assembly **400** comprises the first optical engine **300**, a first semiconductor die **401**, a fiber attachment unit **405** and a package substrate **407**, in accordance with some embodiments.

The first optical engine **300** may be bonded to the package substrate **407** using the first external contacts **303**. In an embodiment the package substrate **407** may be a printed circuit board such as a laminate substrate formed as a stack of multiple thin layers (or laminates) of a polymer material such as bismaleimide triazine (BT), FR-4, ABF, or the like. However, any other suitable substrate, such as a silicon interposer, a silicon substrate, organic substrate, a ceramic substrate, or the like, may alternatively be utilized, and all such redistributive substrates that provide support and connectivity to the first external contacts **303** are fully intended to be included within the scope of the embodiments. The first optical engine **300** may be bonded to the package substrate **407** using, for example, a pick-and-place process to arrange the first optical engine **300** over the package substrate **407**. Once arranged, the first optical engine **300** is electrically coupled to the package substrate **407** for example by performing a suitable bonding process such as a solder reflow process to bond the first external contacts **303** of the first

optical engine **300** to conductive contacts of the package substrate **407**. However, any suitable bonding process may be utilized.

In some embodiments, an optional spacer **411** may be used to control the placement and bonding of the first optical engine **300** to the package substrate **407**. For example, the optional spacer **411** may control a distance the first optical engine **300** is arranged from package substrate **407**. The optional spacer **411** may be formed using any of the dielectric materials and processes suitable to forming the first backfill structure **301**. However, any suitable dielectric materials and techniques may be used to form the optional spacer **411**. According to some embodiments, the optional spacer **411** is formed to the first optical engine **300** prior to bonding the first optical engine **300** to the package substrate **407**. In embodiments in which molding materials and techniques are used to form the first backfill structure **301**, the optional spacer **411** may be formed as an extension of the first backfill structure **301** during molding. In still other embodiments, the optional spacer **411** may be attached to the package substrate **407** prior to bonding the first optical engine **300** to the package substrate **407**. In such cases, the optional spacer **411** may be attached using any suitable materials such as adhesives, adhesive tapes, thermal interface materials (TIM), dielectric or the like and using suitable techniques such as pick-and-place, material extruding, material printing process, photolithography and etching techniques, combinations or the like.

An optional first underfill **409** may be placed between the first optical engine **300** and the package substrate **407**, in accordance with some embodiments. The optional first underfill **409** is a protective material used to cushion and support the first optical engine **300** and the package substrate **407** from operational and environmental degradation, such as stresses caused by the generation of heat during operation. The optional first underfill **409** may be injected or otherwise formed in the space between the first optical engine **300** and the package substrate **407** and may, for example, comprise a liquid epoxy that is dispensed between the first optical engine **300** and the package substrate **407** and then cured to harden. In some embodiments, the optional spacer **411** may be used to control the flow of the optional first underfill **409** during placement.

FIG. **4** further illustrates the attachment of the fiber attachment unit **405** (e.g., fiber holder) to the package substrate **407**. In particular, the first package assembly **400** described herein allows for optical communication with an optical fiber **413** mounted to the fiber attachment unit **405**. In some embodiments, the optical fiber may be mounted from the side of the fiber attachment unit **405** (e.g., in a “horizontal” orientation or “edge coupler” arrangement). In other embodiments, the optical fiber may be mounted from above the fiber attachment unit **405** (e.g., in a “vertical” orientation). The fiber attachment unit **405** may be mounted using a transparent adhesive **415** (e.g., optical glue, epoxy, optical underfill, combinations, or the like). In an active alignment process, the fiber attachment unit **405** is positioned (e.g., using a pick-and-place process) while optical signals are transmitted by the optical fiber **413** to the first optical engine **300** during placement and hardening of the transparent adhesive **415**. For example, optical signals may be transmitted from the optical fiber **413** through the transparent adhesive **415** to the grating coupler **106A** (e.g., edge coupler) and into the first waveguides **105**, wherein the optical signals may be detected by a photodetector **106B** and transmitted as electrical signals into the electronic die **115**. During operation, the backfill structure **301** reduces optical

loss due to any overlapping of the optical signals with the bulk silicon of the semiconductor substrate **103A**. The electronic die **115** may provide indication of proper alignment, for example to a controller for the pick-and-place process, to ensure the fiber attachment unit **405** maintains proper alignment during the placement and hardening of the transparent adhesive **415**. For embodiments in which the fiber attachment unit **405** is placed adjacent the first optical engine **300** in an edge coupler arrangement, the edge coupler arrangement may allow for improved optical coupling, reduced processing cost, or greater design flexibility. In some embodiments, the photonic packages **100** described herein could be considered system-on-chip (SoC) or system-on-integrated-circuit (SoIC) devices.

FIG. **4** additionally illustrates the placement of the first semiconductor die **401** onto the package substrate **407** adjacent the first optical engine **300**. As such, the first semiconductor die **401** is electrically coupled through conductive features (e.g., microbumps, conductive traces, conductive vias, copper traces, combinations, or the like) of the package substrate **407**. In some embodiments, the first semiconductor die **401** is designed to work cooperatively with the first optical engine **300** (as indicated by the directional arrow **419**) to perform a desired function. The first semiconductor die **401** may be, for example, an application specific integrated circuit (ASIC) die, a logic die, a memory die, or the like. In some embodiments, the first semiconductor die **401** may be a packaged device comprising other semiconductor dies and each of the semiconductor dies may be designed to work cooperatively with the first optical engine **300** and/or with one another. In some embodiments, other semiconductor dies and/or packaged devices may be attached to the package substrate **407**. In such embodiments, the other semiconductor dies and/or packaged devices may be designed to work cooperatively with the first optical engine **300** and/or with the first semiconductor die **401**.

For example, in embodiments in which the first semiconductor die **401** and/or other semiconductor dies are logic devices, the first semiconductor die **401** may be a device such as central processing units (CPU), graphics processing unit (GPU), system-on-a-chip (SoC) devices, application processor (AP) devices, microcontrollers, or the like. Additionally, in embodiments in which the first semiconductor die **401** and/or other semiconductor dies are memory devices, these semiconductor dies may be, e.g., a dynamic random access memory (DRAM) die, static random access memory (SRAM) die, hybrid memory cube (HMC) device, high bandwidth memory (HBM) device, or the like. However, any suitable functionality, defined by any suitable structures, is fully intended to be included within the scope of the embodiments.

In an embodiment both of the first semiconductor die **401** and/or the other semiconductor dies may further comprise die contact pads, die passivation layers, die protection layers, and second external contacts **417**. The second external contacts **417** may be any of the contact structures suitable for forming the first external contacts **303** of the first optical engine **300**, as described above. In an embodiment, the second external contacts **417** may be controlled collapse chip connection (C4) bumps. However, any suitable structures may be utilized. Furthermore, the first semiconductor die **401** and/or the other semiconductor dies may be mounted to the package substrate **407** using any of the materials and techniques used to mount the first optical engine **300**. Once mounted, an optional second underfill **421** may be deposited between the package substrate **407** and the first semiconductor die **401** and/or between the package

substrate 407 and the other semiconductor dies. The optional second underfill 421 may be placed using any of the materials and techniques used to place the optional first underfill 409, as set forth above.

FIG. 5 illustrates the first optical engine 300 and the fiber attachment unit 405 comprising an optional feature that allows for passive alignment of the first optical engine 300 and the fiber attachment unit 405 in a co-packaged arrangement 500, according to some embodiments. In particular, FIG. 5 illustrates the first optical engine 300 being aligned and attached to the fiber attachment unit 405 in the co-packaged arrangement 500. As such, the first optical engine 300 and the fiber attachment unit 405 are passively aligned and the co-packaged arrangement 500 may be mounted to the package substrate 407 prior to attaching and actively conducting the optical fiber 413.

FIG. 5 further illustrates the first optical engine 300 comprising an alignment groove 501 and an alignment tab 503, according to some embodiments. In some embodiments, the alignment groove 501 may be formed during a final facet etch process used to form the cavity 201. The alignment groove 501 may be formed using acceptable photolithography and etching techniques to remove materials of the semiconductor substrate 103A, the buried oxide layer 103B, the patterned silicon layer 103C, the gap-fill material 127, and the support substrate 101. In other embodiments, the alignment groove 501 may be formed after the formation of the first backfill structure 301 using acceptable photolithography and etching techniques to remove materials of the first backfill structure 301 along with the other materials of the first optical engine 300. However, still other techniques such as laser-drilling, wafer sawing, combinations or the like may also be utilized. In some embodiments, the alignment groove 501 is formed to a second height H2 of about 60,000 nm. However, any suitable height may be used. A portion of the support substrate 101 that remains after removing materials from the alignment groove 501 forms the alignment tab 503. According to some embodiments, the alignment tab 503 may have a first length of L1 of between about 1,000 nm and about 10,000 nm. The alignment tab 503 may be V-shaped, U-shaped, square-shaped, or the like. However, any suitable length, size, and shape may be used.

FIG. 5 further illustrates the fiber attachment unit 405 comprising an alignment notch 505 corresponding to the alignment tab 503 of the first optical engine 300, according to some embodiments. In embodiments where the fiber attachment unit 405 is formed using a molding compound, the alignment notch 505 may be formed during the molding process used to form the fiber attachment unit 405. In embodiments where the fiber attachment unit 405 is formed using a dielectric materials, the alignment notch 505 may be formed using any suitable photolithography and etching techniques to recess the materials of the fiber attachment unit 405. The alignment notch 505 is formed to a shape acceptable for receiving the alignment tab 503. In some embodiments, the fiber attachment unit 405 and the first optical engine 300 may be assembled and passively aligned using the alignment groove 501, the alignment tab 503, and the alignment notch 505 to form the co-packaged arrangement 500. In some embodiments, a snap-to-fit configuration may be used to fix the fiber attachment unit 405 to the first optical engine 300. However, any suitable configuration may be used. Furthermore, other suitable mechanism (e.g., adhesives, thermal interface materials (TIM), combinations, or the like) may be used to fix the fiber attachment unit 405 to the first optical engine 300 in passive alignment, and all

such configurations and/or mechanisms that fix the fiber attachment unit 405 to the first optical engine 300 are fully intended to be included within the scope of the embodiments.

FIGS. 6-8 illustrate another embodiment of a second optical engine 700 similar to the first optical engine 300, but which utilizes a second backfill structure 701 along with the first backfill structure 301. In this embodiment, and as illustrated in FIG. 6, a second cavity 601 is formed within the BOX substrate 103 adjacent to the first backfill structure 301. The second cavity 601 may be formed using any of the materials and techniques to form the cavity 201, as set forth above.

According to some embodiments, the second cavity 601 is formed in a location along the semiconductor substrate 103A corresponding to electrical components that may be susceptible to electrical leakage during operation (e.g., high bandwidth memory devices, processors, and the like). In other embodiments, the second cavity 601 is formed along the semiconductor substrate 103A corresponding to regions of the second optical engine 700 that may be exposed to undesirable levels of heat during operation (e.g., location for a heat sink, location of thermal hot spots, or the like).

FIG. 7 illustrates the second optical engine 700 after formation of the second backfill structure 701 and attachment of the electronic die 115, according to some embodiments. In particular, once the second cavity 601 has been formed, a suitable backfill material (e.g., dielectric materials, electrical insulators, thermal insulators, thermal conductors, or the like) may be formed within the second cavity 601 using a suitable technique (e.g., chemical vapor deposition (CVD)). Once deposited, the second backfill structure 701 is formed by planarizing the backfill material with the semiconductor substrate 103A and the first backfill structure 301.

For embodiments in which the second cavity 601 is formed in a location corresponding to electrical components, the second cavity 601 may be filled and/or overfilled with a suitable dielectric material. Suitable dielectric materials may include, but are not limited to, electrical insulators, refill oxide materials (e.g., silicon oxide), combinations, or the like. As such, susceptibility to electrical leakage during operation is reduced by the second backfill structure 701 as compared to the susceptibility to electrical leakage of the semiconductor substrate 103A alone.

For embodiments in which the second cavity 601 is formed in a location corresponding to regions exposed to undesirable levels of heat, the second cavity 601 may be filled and/or overfilled with a suitable thermal fill material (e.g., thermal insulators, thermal conductors, or the like). In embodiments where regions of the semiconductor substrate 103A are desired to prevent heat from passing to the second optical engine 700 during operation (e.g., a location corresponding to a thermal hotspot associated with a processing device arranged adjacent the second optical engine 700), a thermal insulator may be used as the thermal fill material. As such, the efficiency of heat transfer is reduced by the second backfill structure 701 as compared to the efficiency of heat transfer of the semiconductor substrate 103A alone. In embodiments where a region of the semiconductor substrate 103A is desired to draw heat away from the second optical engine 700 during operation (e.g., a location intended for a heat sink), a thermal conductor may be used for the thermal fill material. As such, the efficiency of heat transfer is increased by the second backfill structure 701 as compared to the efficiency of heat transfer of the semiconductor substrate 103A alone.

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Although only one optional second backfill structure **701** is illustrated, any suitable number of the optional second backfill structures **603** may be utilized. In some embodiments, different types of materials may be used for the optional second backfill structures **603**. For example, dielectric materials may be used to form one or more of the optional second backfill structures **603** and thermally conductive (and/or thermally insulating) materials may be used to form the remaining optional second backfill structures **603**. However, in still other embodiments, the materials used to form the optional second backfill structures **603** may be the same.

FIG. 7 further illustrates the attachment of the electronic die **115** to the first TIVs **111**, according to some embodiments. The second optical engine **700** is similar to the first optical engine **300** except the electronic die **115** is mounted to a front-side of the second optical engine **700** and is electrically coupled to the photonic die **117** by the first TIVs **111**. In such embodiments, the electronic die **115** is mounted to the device after the backside processing to form the first backfill structure **301** and may be referred to herein as an E-die last process.

In such an E-die last processes, the electronic die **115** may be equipped with third external contacts **703**. The third external contacts **703** may be formed using any of the materials and/or techniques suitable for the first external contacts **303**, set forth above. According to some embodiments, the third external contacts **703** are formed as microbumps. However, any other suitable contacts (e.g., controlled collapse chip connection (C4) bumps) may be utilized. As such, the electronic die **115** may comprise a passivation film, conductive pads **123**, and underbump metallizations (UBMs) for external connection. According to some embodiments, the third external contacts **703** are formed over the UBMs of the electronic die **115**. In other embodiments, the third external contacts **703** are formed over the UBMs of the first TIVs **111**. Once the third external contacts **703** have been formed, the electronic die **115** is placed (e.g., by a pick-n-place process) over the semiconductor substrate **103A** and bonded to the first TIVs **111** using a suitable bonding process (e.g., solder reflow process). However, any suitable placement and bonding processes may be used.

FIG. 7 further illustrates the formation of optional bond pads **803** at the surface of the semiconductor substrate **103A** and at the surface of the package substrate **407**, according to some embodiments. The optional bond pads **803** may be formed to provide an electrical connection between the second optical engine **700** and a subsequently mounted package substrate **407** (not illustrated in FIG. 7 but illustrated and described below with respect to FIG. 8). In an embodiment the optional bond pads **803** are formed of a conductive material such as aluminum, although other suitable materials, such as copper, tungsten, or the like, may be utilized. The optional bond pads **803** may be formed using a process such as CVD or PVD, although other suitable materials and methods may be utilized. Once the material for the optional bond pads **803** has been deposited, the material may be shaped into the optional bond pads **803** using, e.g., a photolithographic masking and etching process. Furthermore, conductive traces and/or conductive features may be formed with the optional bond pads **803** to electrically couple to the third external contacts **703** and/or first TIVs **111** of the second optical engine **700**.

FIG. 8 illustrates a second package assembly **800**, according to some embodiments. The second package assembly

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800 comprises the second optical engine **700**, a wire bond **801**, and the package substrate **407**, in accordance with some embodiments.

The second optical engine **700** may be mounted to the package substrate **407** using a backside bonding process to attach the support substrate **101** to the surface of the package substrate **407**, in accordance with some embodiments. In some embodiments, the second optical engine **700** may be bonded using a suitable bonding material (e.g., adhesives, silicon-to-silicon bonding, combinations, or the like). However, any suitable bonding material and techniques may be used.

Once the second optical engine **700** has been mounted, an optional third underfill material **805** may be placed between the electronic die **115** and the semiconductor substrate **103A**. The optional third underfill material **805** may be placed using any of the materials and techniques used to place the optional first underfill **409**, as set forth above.

The wire bonds **801** are attached to electrically couple the second optical engine **700** and the package substrate **407**. In some embodiments, the wire bonds **801** are attached between bond pads **803** of the semiconductor substrate **103A** and bond pads **803** of the package substrate **407**. In an embodiment, an electronic flame off (EFO) wand may be used to raise the temperature of a gold wire (not individually illustrated in FIG. 8) within a capillary controlled by a wire clamp (also not individually illustrated in FIG. 8). Once the temperature of the gold wire is raised to between about 150° C. and about 250° C., the gold wire is contacted to a bond pad **803** of the semiconductor substrate **103A** to form a first connection and then the gold wire is moved to a bond pad **803** of the package substrate **407** to form a second connection. Once connected, the remainder of the gold wire is separated from the connected portions to form the wire bonds **801**. The connection process may be repeated to form as many connections as desired. As such, the wire bonds **801** may provide signal and power from the package substrate **407** to the second optical engine **700** during operation.

FIG. 8 further illustrates attachment of the optical fiber **413** in an edge coupling configuration with the second optical engine **700**, in accordance with some embodiments. The optical fiber **413** may be aligned and attached to the second optical engine **700** using the fiber attachment unit **405** in any of the active alignment processes or any of the passive alignment processes, as discussed above.

FIG. 9 illustrates a third package assembly **900**, according to some embodiments. The third package assembly **900** comprises a third optical engine **901**, the electronic die **115**, and the package substrate **407**, in accordance with some embodiments. The third optical engine **901** is similar to the second optical engine **700** (shown in FIG. 7) except the electronic die **115** is separate from the third optical engine **901** and the third optical engine **901** is mounted to the package substrate **407** in a front-side mounting process. Instead of being attached to the front-side of the third optical engine **901**, the electronic die **115** is mounted to the package substrate **407**.

According to some embodiments, the third optical engine **901** is mounted to the package substrate **407** using the first external contacts **303**, as set forth above. As such, the photonic die **117** is electrically coupled to the package substrate **407** by the first TIVs **111**. Once the third optical engine **901** has been mounted, the optional first underfill **409** may be placed between the third optical engine **901** and the package substrate **407**, in accordance with some embodiments.

In accordance with some embodiments, the electronic die **115** may be mounted to the package substrate **407** using any of the contacts suitable for forming the third external contacts **703** as set forth above. In some embodiments, the contacts used to mount the electronic die **115** to the package substrate **407** are similar to the first external contacts **303** used to mount the third optical engine **901** to the package substrate **407**. As such, the electronic die **115** is electrically coupled to and cooperates with the photonic die **117** through the conductive features on the package substrate **407** (as indicated by the first directional arrow **905**).

Once the electronic die **115** has been mounted, an optional fourth underfill material **903** may be placed between the electronic die **115** and the package substrate **407**. The optional fourth underfill material **903** may be placed using any of the materials and techniques used to place the optional first underfill **409**, as set forth above.

FIG. **9** further illustrates attachment of the optical fiber **413** in an edge coupling configuration with the third optical engine **901**, in accordance with some embodiments. The optical fiber **413** may be aligned and attached to the third optical engine **901** using the fiber attachment unit **405** in any of the active alignment processes or any of the passive alignment processes, as discussed above.

According to some embodiments, the first semiconductor die **401** (not separately illustrated in FIG. **9**) may be mounted to the package substrate **407** as set forth above. As such, the first semiconductor die **401** may be designed to cooperatively work with and may be electrically coupled to the third optical engine **901** and/or the electronic die **115**.

FIG. **10** illustrates a fourth optical engine **1000**, according to yet some further embodiments. The fourth optical engine **1000** is similar to the first optical engine **300** (shown in FIG. **3**) except the fourth optical engine **1000** comprises second waveguides **1003** and a front side protection layer **1005** instead of the semiconductor substrate **103A**, according to some embodiments.

FIG. **10** further illustrates a third region **1009** of the fourth optical engine **1000** that is highlighted by a dashed circle. The third region **1009** may be referred to herein as the silicon tip of the first waveguides **105** and the second waveguides **1003**. The third region **1009** may provide a location at which optical communication can be conducted through the first waveguides **105** and the second waveguides **1003** during operation of the fourth optical engine **1000**, according to some embodiments.

FIG. **10** further illustrates second TIVs **1011** that extend through the second waveguide **1003** and the front side protection layer **1005**, in accordance with some embodiments. The first external contacts **303** may be formed to the second TIVs **1011** using any of the materials and techniques suitable for attaching the first external contacts **303** to the first TIVs **111**, as set forth above.

FIGS. **11-13** illustrate cross-sectional views of intermediate structures formed during intermediate steps of forming the fourth optical engine **1000**, in accordance with some embodiments. FIG. **11** is similar to the magnified view illustrated in FIG. **1B** except without having formed the first TIVs **111** into the semiconductor substrate **103A**. FIG. **11** further illustrates a fourth region **1103** highlighted by a dashed rectangle. FIGS. **12** and **13** illustrate magnified views of the fourth region **1103** during further processing of the intermediate structure **1100** illustrated in FIG. **11**, according to some embodiments.

FIG. **12** illustrates the formation of a second waveguide material layer **1201** (e.g., silicon layer), according to some embodiments. The second waveguide material layer **1201**

may be formed by initially removing the semiconductor substrate **103A** and thinning the buried oxide layer **103B**. According to some embodiments, the semiconductor substrate **103A** may be removed using a planarization process such as a chemical mechanical planarization (CMP), grinding technique, etching process (e.g., wet etch), combinations, or the like. However, any suitable process may be used to remove the semiconductor substrate **103A**. Furthermore, because the semiconductor substrate **103A** is removed, formation of the first TIVs **111** may be omitted according to some embodiments. In other embodiments, the first TIVs **111** may be formed to extend through the passivation layer **109**, the patterned silicon layer **103C** and into and/or through the buried oxide layer **103B** but not to extend into the semiconductor substrate **103A**.

Once the semiconductor substrate **103A** has been removed, a subsequent thinning process may be used to reduce a thickness of the buried oxide layer **103B**. According to some embodiments, the thickness of the buried oxide layer **103B** may be reduced by performing a subsequent chemical mechanical planarization (CMP) using etchants and abrasives suitable for removing the material of the buried oxide layer **103B** and exposing a surface of the buried oxide layer **103B**. However, any suitable thinning process may be used. According to some embodiments, the buried oxide layer **103B** may be reduced to a third thickness **Th3** that is less than about 100 μm , such as 2 μm . However, any suitable thickness may be used.

Once the thickness of the buried oxide layer **103B** has been reduced, the second waveguide material layer **1201** is formed adjacent the exposed surface of the buried oxide layer **103B**. According to some embodiments, the second waveguide material layer **1201** is a material such as a nitride, silicon nitride, polymer, combinations, or the like and is deposited using a deposition technique such as chemical vapor deposition (CVD), atomic layer deposition (ALD), or the like. However, any suitable materials and deposition techniques may be used. Furthermore, the second waveguide material layer **1201** is deposited to a fourth thickness **Th4** of between about 0.1 μm and about 0.4 μm . However, any suitable thickness may be used.

FIG. **13** illustrates that, once deposited, the second waveguide material layer **1201** is patterned to form first waveguides **1003A**, according to some embodiments. The first waveguides **1003A** may be formed using any of the photolithography and etching techniques suitable for patterning the first waveguides **105**, as set forth above. Once the first waveguides **1003A** have been formed, a first oxide protection layer **1005A** is formed adjacent the first waveguides **1003A** using any of the materials and techniques suitable for forming and planarizing the buried oxide layer **103B** as set forth above. The first oxide protection layer **1005A** may be formed and planarized to a fifth thickness **Th5** of between about 0.1 μm and about 0.4 μm . However, any suitable thickness may be used.

According to some embodiments, optional second waveguides **1003B** are formed adjacent the exposed surface of the first oxide protection layer **1005A**. The optional second waveguides **1003B** may be formed using any of the materials and techniques suitable for forming the first waveguides **1003A**. Once the optional second waveguides **1003B** have been formed, a second oxide protection layer **1005B** is formed adjacent the second waveguides **1003B** using any of the materials and techniques suitable for forming and planarizing the buried oxide layer **103B** as set forth above. The second oxide protection layer **1005B** may be formed and planarized to a sixth thickness **Th6** of between about 4 μm

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and about 25 μm , such as about 5 μm . However, any suitable thickness may be used. The first oxide protection layer **1005A** and the second oxide protection layer **1005B** may be collectively referred to herein as the front side protection layer **1005**.

The first waveguides **1003A** and the second waveguides **1003B** may be collectively referred to herein as the second waveguides **1003**. The second waveguides **1003** allow for optical communications to be coupled to/from the first waveguides **105**. In embodiments where the optional second waveguides **1003B** are omitted, the second oxide protection layer **1005B** is also omitted. In such embodiments, the first oxide protection layer **1005A** is formed to the seventh thickness Th_7 of between about 5 μm and about 25 μm . However, any suitable thickness may be used.

Openings may be formed through the front side protection layer **1005**, the second waveguides **1003**, and/or the buried oxide layer **103B** to expose the contacts **113** embedded within the photonic die **117**. Once the contacts **113** have been exposed, the second TIVs **1011** are formed within the openings. The second TIVs **1011** may be formed using any of the materials and methods used to form the first TIVs **111**, as set forth above. In some embodiments, the second TIVs **1011** may be formed as copper vias.

FIG. **14** illustrates a fourth package assembly **1400**, according to yet some further embodiments which utilize a cavity **1401**. The fourth package assembly **1400** comprises the fourth optical engine **1000** (see, e.g., FIG. **10**), the fiber attachment unit **405**, and the package substrate **407**, in accordance with some embodiments. The fourth optical engine **1000** may be mounted to the package substrate **407** using the first external contacts **303** and the optional spacer **411** using any of the methods set forth above for mounting the first optical engine **300**, as set forth above with regard to FIG. **4**. As such, the photonic die **117** is electrically coupled to the package substrate **407** by the second TIVs **1011**. Once the fourth optical engine **1000** has been mounted, the optional first underfill **409** may be placed between the fourth optical engine **1000** and the package substrate **407**, in accordance with some embodiments.

FIG. **14** further illustrates attachment of the optical fiber **413** and the fiber attachment unit **405** in an active alignment process with the fourth optical engine **1000**, in accordance with some embodiments. FIG. **14** further illustrates the transparent adhesive **415** placed or formed within the cavity **1401** of the package substrate **407**. As such, the displacement of the transparent adhesive **415** between the fiber attachment unit **405** and the package substrate **407** may be controlled by the available space of the cavity **1401** during the active alignment process. Although the active alignment process is illustrated in FIG. **14**, the optical fiber **413** may be aligned and attached to the fourth optical engine **1000** using the fiber attachment unit **405** in any of the active alignment processes or any of the passive alignment processes, as discussed above.

According to some embodiments, the first semiconductor die **401** (not separately illustrated) may also be mounted to the package substrate **407** as described above with regard to the first package assembly **400**. As such, the first semiconductor die **401** may be designed to cooperatively work with and may be electrically coupled to the fourth optical engine **1000** through the package substrate **407**.

FIGS. **15-17** illustrate cross-sectional views of intermediate structures formed during intermediate steps of forming a fifth optical engine **1800** (see FIG. **18**), in accordance with some embodiments. In these embodiments, the fifth optical

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engine **1800** may be formed by initially forming the intermediate structure illustrated in FIG. **11**.

In particular, FIG. **15** illustrates a first photonic integrated circuit **1500** that is similar to the intermediate structure shown in FIG. **12** except prior to having formed the second waveguide material layer **1201** adjacent the buried oxide layer **103B**. As such, any of the materials and processes suitable for forming the intermediate structure illustrated in FIG. **12** may be used to form the first photonic integrated circuit **1500**. FIG. **15** further illustrates a magnified view of the first waveguides **105** and the buried oxide layer **103B** after having been thinned.

Once the buried oxide layer **103B** has been thinned, first TIVs **111** and/or contacts may be formed through the buried oxide layer **103B** and the first waveguides **105** and electrically coupled to the contacts **113** of the photonic die **117** in order to provide electrical connectivity between the first photonic integrated circuit **1500** and other structures. In an embodiment, connection pads **1501** are formed over the first TIVs **111** using a conductive material such as aluminum, although other suitable materials, such as copper, tungsten, or the like, may alternatively be utilized. The connection pads **1501** may be formed using a process such as CVD, although other suitable materials and methods may alternatively be utilized. Once the material for the connection pads **1501** has been deposited, the material may be shaped into the connection pads **1501** using, e.g., a photolithographic masking and etching process.

FIG. **16** illustrates the formation of a pluggable modularized device which includes the first photonic integrated circuit **1500** and which also comprises a first carrier substrate **1601**, a first adhesive layer **1603**, and the formation of through molding vias (TMVs) **1605** over the first adhesive layer **1603**. The first carrier substrate **1601** comprises, for example, silicon based materials, such as glass or silicon oxide, or other materials, such as aluminum oxide, combinations of any of these materials, or the like. The first carrier substrate **1601** is planar in order to accommodate an attachment of the first photonic integrated circuit **1500**.

The first adhesive layer **1603** is placed on the first carrier substrate **1601** in order to assist in the adherence of overlying structures (e.g., the first photonic integrated circuit **1500**). In an embodiment the first adhesive layer **1603** may comprise a die attach film, such as an ultra-violet glue, which loses its adhesive properties when exposed to ultra-violet light. However, other types of adhesives, such as pressure sensitive adhesives, radiation curable adhesives, epoxies, combinations of these, or the like, may also be used. The first adhesive layer **1603** may be placed onto the first carrier substrate **1601** in a semi-liquid or gel form, which is readily deformable under pressure.

The TMVs **1605** are formed over the first adhesive layer **1603**, and comprise a first seed layer (not shown separately from the TMVs **1605**). The first seed layer is formed over the first adhesive layer **1603**, and is a thin layer of a conductive material that aids in the formation of a thicker layer during subsequent processing steps. The first seed layer may comprise a layer of titanium about 1,000 Å thick followed by a layer of copper about 5,000 Å thick. The first seed layer may be created using processes such as sputtering, evaporation, or PECVD processes, depending upon the desired materials. The first seed layer may be formed to have a thickness of between about 0.3 μm and about 1 μm , such as about 0.5 μm .

Once the first seed layer has been formed, a photoresist (not separately illustrated) is placed and patterned over the first seed layer. In an embodiment the photoresist may be placed on the first seed layer using, e.g., a spin coating

technique to a height of between about 50 μm and about 250 μm , such as about 120 μm . Once in place, the photoresist may then be patterned by exposing the photoresist to a patterned energy source (e.g., a patterned light source) so as to induce a chemical reaction, thereby inducing a physical change in those portions of the photoresist exposed to the patterned light source. A developer is then applied to the exposed photoresist to take advantage of the physical changes and selectively remove either the exposed portion of the photoresist or the unexposed portion of the photoresist, depending upon the desired pattern.

In an embodiment the pattern formed into the photoresist is a pattern for the TMVs **1605**. The TMVs **1605** are formed in such a placement as to allow electrical paths to be located adjacent to the subsequently placed first photonic integrated circuit **1500** and may be formed with a pitch of less than about 40 μm . However, any suitable arrangement for the pattern of TMVs **1605**, such as by being located such that one or more first photonic integrated circuits **1500** are placed on opposing sides of the TMVs **1605**, may be utilized.

In an embodiment the TMVs **1605** are formed within the photoresist and comprise one or more conductive materials, such as copper, tungsten, other conductive metals, or the like. The TMVs **1605** may be formed, for example, by electroplating, electroless plating, or the like. In an embodiment, an electroplating process is used wherein the first seed layer and the photoresist are submerged or immersed in an electroplating solution. The first seed layer surface is electrically connected to the negative side of an external DC power supply such that the first seed layer functions as the cathode in the electroplating process. A solid conductive anode, such as a copper anode, is also immersed in the solution and is attached to the positive side of the power supply. The atoms from the anode are dissolved into the solution, from which the cathode, e.g., the first seed layer, acquires the dissolved atoms, thereby plating the exposed conductive areas of the first seed layer within the opening of the photoresist.

Once the TMVs **1605** have been formed using the photoresist and the first seed layer, the photoresist may be removed using a suitable removal process. In an embodiment, a plasma ashing process may be used to remove the photoresist, whereby the temperature of the photoresist may be increased until the photoresist experiences a thermal decomposition and may be removed. However, any other suitable process, such as a wet strip, may be utilized. The removal of the photoresist may expose the underlying portions of the first seed layer.

Once exposed a removal of the exposed portions of the first seed layer may be performed. In an embodiment the exposed portions of the first seed layer (e.g., those portions that are not covered by the TMVs **1605**) may be removed by, for example, a wet or dry etching process. For example, in a dry etching process reactants may be directed towards the first seed layer using the TMVs **1605** as masks. In another embodiment, etchants may be sprayed or otherwise put into contact with the first seed layer in order to remove the exposed portions of the first seed layer. After the exposed portion of the first seed layer has been etched away, a portion of the first adhesive layer **1603** is exposed between the TMVs **1605**.

FIG. **16** additionally illustrates a placement of the first photonic integrated circuit **1500** onto the first adhesive layer **1603**, according to some embodiments. In some embodiments, the first photonic integrated circuit **1500** is placed with a front side facing the first carrier substrate **1601** and is attached by the first adhesive layer **1603**. For example, a

pick and place tool may be used to place the first photonic integrated circuit **1500** over the first carrier substrate **1601**. However, any suitable method may be used.

FIG. **16** also illustrates an encapsulation of the TMVs **1605** and the first photonic integrated circuit **1500**. The encapsulation may be performed in a molding device (not individually illustrated in FIG. **16**), which may comprise a top molding portion and a bottom molding portion separable from the top molding portion. When the top molding portion is lowered to be adjacent to the bottom molding portion, a molding cavity may be formed for the first carrier substrate **1601**, the TMVs **1605**, and the first photonic integrated circuit **1500**.

During the encapsulation process the top molding portion may be placed adjacent to the bottom molding portion, thereby enclosing the first carrier substrate **1601**, the TMVs **1605**, and the first photonic integrated circuit **1500** within the molding cavity. Once enclosed, the top molding portion and the bottom molding portion may form an airtight seal in order to control the influx and outflux of gasses from the molding cavity. Once sealed, an encapsulant **1607** may be placed within the molding cavity. The encapsulant **1607** may be a molding compound resin such as polyimide, PPS, PEEK, PES, a heat resistant crystal resin, combinations of these, or the like. The encapsulant **1607** may be placed within the molding cavity prior to the alignment of the top molding portion and the bottom molding portion, or else may be injected into the molding cavity through an injection port.

Once the encapsulant **1607** has been placed into the molding cavity such that the encapsulant **1607** encapsulates the first carrier substrate **1601**, the TMVs **1605**, and the first photonic integrated circuit **1500**, the encapsulant **1607** may be cured in order to harden the encapsulant **1607** for optimum protection. While the exact curing process is dependent at least in part on the particular material chosen for the encapsulant **1607**, in an embodiment in which molding compound is chosen as the encapsulant **1607**, the curing could occur through a process such as heating the encapsulant **1607** to between about 100° C. and about 130° C. for about 60 sec to about 3000 sec. Additionally, initiators and/or catalysts may be included within the encapsulant **1607** to better control the curing process.

However, as one having ordinary skill in the art will recognize, the curing process described above is merely an exemplary process and is not meant to limit the current embodiments. Other curing processes, such as irradiation or even allowing the encapsulant **1607** to harden at ambient temperature, may be used. Any suitable curing process may be used, and all such processes are fully intended to be included within the scope of the embodiments discussed herein.

A thinning of the encapsulant **1607** may be performed in order to expose the TMVs **1605** and backside of the first photonic integrated circuit **1500** for further processing. The thinning may be performed, e.g., using a mechanical grinding or chemical mechanical polishing (CMP) process whereby chemical etchants and abrasives are utilized to react and grind away the encapsulant **1607** and/or the backside of the first photonic integrated circuit **1500** until the TMVs **1605** and the first photonic integrated circuit **1500** have been exposed. As such, the first photonic integrated circuit **1500** and the TMVs **1605** may have a planar surface that is also coplanar with the encapsulant **1607**.

However, while the CMP process described above is presented as one illustrative embodiment, it is not intended to be limiting to the embodiments. Any other suitable

removal process may be used to thin the encapsulant **1607** and/or the backside of the first photonic integrated circuit **1500** and expose the TMVs **1605**. For example, a series of chemical etches may be utilized. This process and any other suitable process may be utilized to thin the encapsulant **1607** and/or the backside of the first photonic integrated circuit **1500**, and all such processes are fully intended to be included within the scope of the embodiments.

Once the TMVs **1605** and the first photonic integrated circuit **1500** have been embedded in the molding compound, a front side redistribution structure **1609** may be formed in electrical connection with the TMVs **1605** on the coplanar surface of the first photonic integrated circuit **1500**, the TMVs **1605** and the encapsulant **1607**, according to some embodiments. In an embodiment the front side redistribution structure **1609** may be formed using a series of alternating layers of front side dielectric layers **1611** and front side redistribution layers **1613**. In an embodiment the front side dielectric layers **1611** may be a polymer based dielectric material such as polybenzoxazole (PBO), although any suitable material, such as polyimide or a polyimide derivative, may be utilized. The front side dielectric layers **1611** may be placed using, e.g., a spin-coating process to a thickness of between about 5 μm and about 25 μm , such as about 7 μm , although any suitable method and thickness may be used.

After each of the front side dielectric layers **1611** has been placed, the front side dielectric layer **1611** may be patterned in order to expose conductive portions of the underlying structures (e.g., the TMVs **1605**). In an embodiment the front side dielectric layers **1611** may be patterned using, e.g., a photolithographic masking and etching process, whereby a photoresist is placed, exposed, and developed, and the photoresist is then used as a mask during an anisotropic etching process. However, any suitable process for patterning the front side dielectric layers **1611** may be utilized.

Once the front side dielectric layer **1611** has been patterned, the front side redistribution layer **1613** may be formed to make contact with the underlying conductive regions. In an embodiment the front side redistribution layer **1613** may be formed by initially forming a second seed layer of a titanium copper alloy through a suitable formation process such as CVD or sputtering. Once the second seed layer has been deposited, a photoresist (not separately illustrated) may be placed onto the second seed layer to prepare for a formation of the front side redistribution layer **1613**. Once the photoresist has been formed and patterned, a conductive material, such as copper, may be formed on the second seed layer through a deposition process such as plating. The conductive material may be formed to have a thickness of between about 1 μm and about 10 μm , such as about 5 μm . However, while the material and methods discussed are suitable to form the conductive material, these materials are merely exemplary. Any other suitable materials, such as AlCu or Au, and any other suitable processes of formation, such as CVD or PVD, may be used to form the front side redistribution layer **1613**.

Once the conductive material has been formed, the photoresist may be removed through a suitable removal process such as ashing, wet etching, or plasma etching. Additionally, after the removal of the photoresist, those portions of the second seed layer that were covered by the photoresist may be removed through, for example, a suitable etch process using the conductive material as a mask.

Once the front side redistribution layer **1613** has been formed, further front side dielectric layer **1611** and further front side redistribution layer **1613** may be formed one over

the other in alternating fashion electrically coupling the front side redistribution layers **1613** to one another through the front side dielectric layers **1611** until a desired topmost front side dielectric layer **1611** is formed. The further front side dielectric layers **1611** and the further front side redistribution layers **1613** may be formed using any of the materials and processes set forth above. However, any suitable material and method of deposition may be utilized. In accordance with some embodiments, the TMVs **1605** are electrically coupled to conductive features of the topmost redistribution layer **1613** by the front side redistribution structure **1609**.

In a particular embodiment the front side redistribution structure **1609** may be formed such that the front side redistribution structure **1609** has a reduced pitch between conductive elements. For example, the conductive elements may be formed to have a pitch of between about 4 μm and about 20 μm . However, any suitable pitch may be utilized.

FIG. 17 illustrates a transfer of the structure to a second carrier substrate **1701** and a removal of the first carrier substrate **1601**. In an embodiment, the front side redistribution structure **1609** may be attached to the second carrier substrate **1701** using, e.g., a second adhesive layer **1703**. The second carrier substrate **1701** and the second adhesive layer **1703** may be similar to the first carrier substrate **1601** and the first adhesive layer **1603** (described above with respect to FIG. 16), although any suitable structures and any suitable adhesives may be utilized.

Once the structure has been attached to the second carrier substrate, conductive studs **1705** may be formed over and electrically coupled to the TMVs **1605** and/or over the connection pads **1501** for external connection to the first photonic integrated circuit **1500**. The conductive studs **1705** may be formed using a material such as copper, aluminum, combinations, or the like, by plating the material onto a seed layer partially covered by a photoresist. Once the conductive studs **1705** have been formed, the photoresist is removed and then the seed layer is etched using the conductive studs **1705** as a mask. However, any suitable materials and methods may be utilized.

FIG. 17 further illustrates the formation of a polymer waveguide **1707** over the front side of the first photonic integrated circuit **1500** to optically communicate with the first waveguide **105** during operation. According to some embodiments, the polymer waveguide **1707** may be formed using acceptable photolithography and etching techniques. For example, the polymer waveguide **1707** may be formed by initially forming a photoresist adjacent the thinned buried oxide layer **103B** and overlying the conductive studs **1705** and exposed surfaces of the encapsulant **1607**. Once formed, the photoresist is patterned with an opening corresponding to the first waveguide **105** and to expose a region over an edge portion of the encapsulant **1607**. In some embodiments, the region over the edge portion of the encapsulant **1607** corresponds to a designated location for optical communications external to the first photonic integrated circuit **1500** during operation. Once patterned, the photoresist may be used as a mask to deposit the second waveguide material layer **1201** adjacent the buried oxide layer **103B** and over the edge portion of the encapsulant **1607**.

In an embodiment the polymer waveguide **1707** may be any type of waveguide, such as a planar waveguide or a channel waveguide, and may comprise two different materials, a core material and a cladding material, in which the core material has a refractive index higher than the cladding material. In an embodiment, the core material and the cladding material comprise a combination of polymer materials, such as poly(methylmethacrylate) (PMMA), polysty-

rene (PS), polycarbonate, polyurethane, benzocyclobutane, perfluorovinyl ether cyclopolymer, tetrafluoroethylene, perfluorovinyl ether copolymer, silicone, fluorinated poly(arylene ether sulfide), poly(pentafluorostyrene), fluorinated dendrimers, fluorinated hyperbranched polymers, or the like. In another embodiment, the core material and the cladding material may comprise deuterated and halogenated polyacrylates, fluorinated polyimides, perfluorocyclobutyl aryl ether polymers, nonlinear optical polymers, or the like.

The core material and the cladding material of the polymer waveguide **1707** may be formed, e.g., by initially placing each layer or combination of layers within the opening of the photoresist using a process such as spin coating, doctor blading, extrusion, lamination, or the like. As each layer of the polymer waveguide **1707** is formed, the layer may be patterned and shaped in order to control and direct optical signals during operation to and from the first waveguide **105**. For example, as each layer of material of the polymer waveguide **1707** is formed, a series of one or more etches such as wet etches or dry etches, may be used to shape the layers of material as desired. However any suitable methods may be utilized. According to some embodiments, the polymer waveguide **1707** may be formed to the eighth thickness T_{h8} of between about 3 μm and about 10 μm . However, any suitable thickness may be used.

Once the polymer waveguide **1707** has been formed, the photoresist may be removed using a removal process such as ashing. However, any suitable removal process may be used.

FIG. **18** illustrates an fifth optical engine **1800**, according to some embodiments. In particular, FIG. **18** illustrates a formation of a backside redistribution structure **1801** formed over the conductive studs **1705**, the polymer waveguide **1707**, the encapsulant **1607**, and the first photonic integrated circuit **1500**, in accordance with some embodiments.

The backside redistribution structure **1801** may be formed using a series of alternating layers of backside dielectric layers **1803** and backside redistribution layers **1805** that are similar to the formation of the front side redistribution structure **1609** described above. The backside dielectric layers **1803** and the backside redistribution layers **1805** may be formed using any of the materials and processes used to form the front side dielectric layers **1611** and the front side redistribution layers **1613**, respectively.

Additionally, a topmost layer of the backside dielectric layers **1803** may be patterned to form openings and expose areas of the underlying backside redistribution layer **1805**. Contact pads **1807** may be formed within the openings. In an embodiment the contact pads **1807** may comprise aluminum, but other materials, such as copper, may be used. The contact pads **1807** may be formed using a deposition process, such as sputtering, to form a layer of material (not shown) that fills the openings within the backside dielectric layers **1803**. Once filled, the material may be planarized with the backside dielectric layers **1803** using, for example, a chemical mechanical polishing process. However, any other suitable process may be utilized to form the contact pads **1807**. Once formed, the backside redistribution structure **1801** electrically couples the conductive studs **1705** and the first photonic integrated circuit **1500** to the contact pads **1807** for external connection to overlying components.

FIG. **18** further illustrates the placement and mounting of the first semiconductor die **401** to the backside redistribution structure **1801**. The first semiconductor die **401** may be placed into contact with the contact pads **1807** and in electrical contact with the first photonic integrated circuit **1500** and/or the TMVs **1605**. As such, the first semiconductor die **401** may be designed to cooperatively work with and

may be electrically coupled to the first photonic integrated circuit **1500** through the backside redistribution structure **1801**. In an embodiment the first semiconductor die **401** may further comprise the second external contacts **417** (e.g., controlled collapse chip connection (C4) bumps). However, any suitable materials and/or structures may be utilized for the second external contacts **417**.

The first semiconductor die **401** may be placed onto the contact pads **1807** using, e.g., a pick and place process. However, any other method of placing the first semiconductor die **401** may be used. Once in physical contact, a bonding process may be performed in order to bond the first semiconductor die **401** with the contact pads **1807**. For example, in an embodiment in which the contact pads **1807** are solder bumps, the bonding process may comprise a reflow process whereby the temperature of the contact pads **1807** is raised to a point where the contact pads **1807** will liquefy and flow, thereby bonding the first semiconductor die **401** to the contact pads **1807** once the contact pads **1807** re-solidifies.

FIG. **18** further illustrates a placement of an optional fifth underfill **1809** between the first semiconductor die **401** and the backside redistribution structure **1801**. In an embodiment the optional fifth underfill **1809** is a protective material used to cushion and support the first semiconductor die **401** and the backside redistribution structure **1801** from operational and environmental degradation, such as stresses caused by the generation of heat during operation. The optional fifth underfill **1809** may be injected or otherwise formed in the space between the first semiconductor die **401** and the backside redistribution structure **1801** and may, for example, comprise a liquid epoxy that is dispensed between the first semiconductor die **401** and the backside redistribution structure **1801** and then cured to harden.

FIG. **18** also illustrates formation of the UBMs and the first external contacts **303**, according to some embodiments. The UBMs and the first external contacts **303** may be formed by initially forming openings in the bottommost layer of the front side dielectric layers **1611** and exposing the front side redistribution layers **1613**. The UBMs may be formed in the openings and in electrical contact with the front side redistribution layers **1613**. The UBMs may be formed using any of the materials and processes disclosed above for forming UBMs. The first external contacts **303** are formed and/or placed over the UBMs, and a reflow process may be performed. However, any suitable methods and materials may be utilized.

According to some embodiments, the fifth optical engine **1800** is formed as a standalone package device with the polymer waveguide **1707** located in an edge coupler configuration for optical communications during operation. As such, the fifth optical engine **1800** may be used in various package assemblies.

FIG. **19** illustrates a fifth package assembly **1900**, according to still further embodiments. The fifth package assembly **1900** comprises the fifth optical engine **1800**, the fiber attachment unit **405**, and the package substrate **407**, in accordance with some embodiments. The fifth optical engine **1800** may be mounted to the package substrate **407** using the first external contacts **303** and the optional spacer **411** using any of the methods set forth above for mounting the first optical engine **300**. As such, the first photonic integrated circuit **1500** is electrically coupled to the package substrate **407** by the TMVs **1605**. Once the integrated optical engine device **1800** has been mounted, an optional sixth underfill **1901** may be placed between the fifth optical engine **1800** and the package substrate **407**, in accordance with some embodiments.

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FIG. 19 further illustrates attachment of the optical fiber 413 and the fiber attachment unit 405 in an active alignment process with the fifth optical engine 1800, in accordance with some embodiments. As such, the first photonic integrated circuit 1500 may optically communicate between the polymer waveguide 1707 and the optical fiber 413 in an edge coupler configuration during operation. FIG. 19 also illustrates the transparent adhesive 415 formed between the fifth optical engine 1800, the fiber attachment unit 405, and the package substrate 407. Although the active alignment process is illustrated in FIG. 19, the optical fiber 413 may be aligned and attached to the fifth optical engine 1800 using the fiber attachment unit 405 in any of the active alignment processes or any of the passive alignment processes, as discussed above.

FIG. 20 illustrates a sixth package assembly 2000 comprising a first integrated optical engine device 1800A and a second integrated optical engine device 1800B that are co-packaged with the package substrate 407, according to some embodiments. The first integrated optical engine device 1800A and the second integrated optical engine device 1800B are arranged over the package substrate 407 with polymer waveguides aligned, e.g., in a pick-and-place process. For example, a first polymer waveguide 1707A of the first integrated optical engine device 1800A is aligned with a second polymer waveguide 1707B of the second integrated optical engine device 1800B to form an optical interconnect 2001. The first integrated optical engine device 1800A and the second integrated optical engine device 1800B are mounted to the package substrate 407 by performing a solder reflow process on the first external contacts 303, according to some embodiments. However, any methods suitable for mounting the first external contacts 303 to the package substrate 407, as set forth above may also be used. Once mounted, a seventh underfill 2003 may be placed between the first integrated optical engine device 1800A, the second integrated optical engine device 1800B, and the package substrate 407.

During operation, die-to-die optical communications may be performed between the first integrated optical engine device 1800A and the second integrated optical engine device 1800B over the optical interconnect 2001. Furthermore, the first integrated optical engine device 1800A and the second integrated optical engine device 1800B may receive power and signals from the package substrate 407 during operation and may conduct die-to-die electrical communications through conductive features of the package substrate 407 during operation (as indicated by the first directional arrow 905).

FIGS. 21-23 illustrate structures that are formed during intermediate steps of forming a seventh package assembly 2400 (see FIG. 24), according to still further embodiments. The seventh package assembly 2400 comprises a first photonic interconnect structure 2100, a first embedded optical engine 2201A and a second embedded optical engine 2201B that are co-packaged with the first photonic interconnect structure 2100, according to some embodiments.

The first photonic interconnect structure 2100 comprises a first photonic die interconnect 2101A and a second photonic die interconnect 2101B, according to some embodiments. The first photonic die interconnect 2101A and the second photonic die interconnect 2101B may be collectively referred to herein as the photonic die interconnects 2101. The photonic die interconnects 2101 may also be referred to herein as the photonic interconnect layer. Furthermore, any suitable number of the photonic die interconnects 2101 may be formed within the first photonic interconnect structure

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2100 and all such photonic interconnect structures are fully intended to be included within the scope of the embodiments.

According to some embodiments, the first photonic interconnect structure 2100 may be formed by initially forming the box substrate 103, as set forth above. Once the patterned silicon layer 103C has been formed, the first waveguides 105 and first photonic components 107 (e.g., grating couplers 106A, photodetectors 106B, modulators 106C, combinations, or the like) may be formed within the patterned silicon layer 103C, as described above. Once the first waveguides 105 and first photonic components 107 have been formed, the dielectric layers 119 and the conductive feature 121, and through structure vias TSVs 2105 may be formed over and/or into the semiconductor substrate 103A. The dielectric layers 119 and the conductive features 121 may be formed over the BOX substrate 103 as set forth above. The TSVs 2105 are similar to the first TIVs 111 and may be formed through the dielectric layers 119 and into the BOX substrate 103 using any of the materials and process suitable for forming the first TIVs 111. Once the TSVs 2105 have been formed, contacts 113 of the photonic die 117 and/or conductive pads 123 of the first photonic interconnect structure 2100 may be formed within a topmost layer of the dielectric layers 119 and in electrical connection to the conductive features 121 and/or the TSVs 2105.

FIG. 21 further illustrates a formation of optical windows 2103 through the dielectric layers 119, according to some embodiments. The optical windows 2103 are formed by initially forming openings through the dielectric layers 119 over locations of grating couplers 106A in the first waveguides 105. Once formed, the openings are filled with optical materials transparent to the relevant wavelengths of light (e.g., silicon oxide, optical glue (e.g., optically clear adhesive (OCA)), optical resins, optical glass, optical ceramics, combinations, or the like) to be used instead of opaque materials that are optical isolators (e.g., opaque dielectrics, encapsulant, molding compounds, or the like). The optical windows 2103 may also be referred to herein as optical feedthroughs or optical passageways. In some embodiments, the optical material used to form the optical windows 2103 is an index-matching material that matches an index of a material of an overlying structure (e.g., embedded optical engines 2201; see FIG. 22).

In some embodiments, the optical windows 2103 are located in some regions of the photonic die interconnects 2101 that are substantially free of the conductive feature 121, the contacts 113, the conductive pads 123, and the interconnect TIVs 111 in order to allow transmission of optical power and/or optical signals through the dielectric layers 119. For example, these regions may extend between the grating couplers 106A and the overlying structure (e.g., embedded optical engines 2201) to allow optical power or optical signals to be coupled from the first waveguides 105 of the photonic die interconnects 2101 into the embedded optical engines 2201 and/or to be coupled from the embedded optical engines 2201 into the first waveguides 105 of the photonic die interconnects 2101. In some cases, a thinner photonic die 117 may allow for more efficient optical coupling between the grating couplers 106A and the overlying structures (e.g., embedded optical engines 2201).

FIG. 22 illustrates the attachment of the embedded optical engines 2201, a second semiconductor die 2203, and a sacrificial block 2205 to the photonic die interconnects 2101 according to some embodiments. The embedded optical engines 2201 are similar to the first optical engine 300 except die pads 2206 are formed in electrical connection

with the first TTVs **111** for external connection instead of the first external contacts **303**. In some embodiments, a hybrid bonding process may be used with, for example, a pick-and-place process to mount the first embedded optical engine **2201A** and the second embedded optical engine **2201B** to the first photonic die interconnect **2101A** and the second photonic die interconnect **2101B**, respectively. As such, the die pads **2206** and the semiconductor substrate **103A** of the embedded optical engines **2201** are bonded to the conductive pads **123** and the dielectric layers **119** of the photonic die interconnects **2101**, respectively. During the hybrid bonding process, the first backfill structure **301** of the embedded optical engine **2201** is also bonded to the dielectric layers **119** and/or the optical windows **2103** of the photonic die interconnects **2101**. In some embodiments, an optical adhesive (e.g., optical clear glue) may be used during the hybrid bonding process to assist in the bonding of the first backfill structures **301** to the optical windows **2103**.

FIG. **22** further illustrates an optional interfacial layer **2207** of the embedded optical engines **2201**, according to some embodiments. In some embodiments, the optional interfacial layer **2207** may be disposed between the support substrate **101** and the coplanar surface of the gap-fill material **127** and the electronic die **115**. The optional interfacial layers **2207** may be an optical dielectric material that is transparent to the relevant wavelengths of light and may be formed using any of the materials and methods that are suitable for forming the gap-fill material **127** set forth above. In some embodiments, the optional interfacial layer **2207** is an index-matching material that matches an optical index of the gap-fill material **127** to an optical index of the support substrate **101**. As such, the optional interfacial layer **2207** may prevent optical loss and/or distortion of optical communications passing between the gap-fill material **127** and the support substrate **101** during operation. According to some embodiments, the optional interfacial layer **2207** may also be added to a backside of the support substrate **101** for subsequent connection of an optical fiber **413** (see FIG. **24**). In such embodiments, the optional interfacial layer **2207** may be an index-matching material that matches an optical index of the optical fiber **413** to the optical index of the support substrate **101**. As such, the optional interfacial layer **2207** may prevent optical loss and/or distortion of optical communications passing between the optical fiber **413** and the support substrate **101** during operation.

The second semiconductor die **2203** is similar to the first semiconductor die **401** except die pads **2206** are provided for external connection instead of the second external contacts **417** (shown in FIG. **4**). According to some embodiments, the die pads **2206** of the second semiconductor die **2203** may be bonded to conductive pads **123** of the first photonic interconnect structure **2100** in a hybrid bonding process. As such, dielectric material of the second semiconductor die **2203** (e.g., encapsulant, molding compound, silicon oxide, combinations, or the like) that is exposed between the die pads **2206** may also be bonded to the dielectric layers **119** of the photonic die **117** during the hybrid bonding process. According to some embodiments, the second semiconductor die **2203** is an ASIC device (e.g., multi-host controller, switch, or the like) that is designed to cooperate during operation with two or more of the embedded optical engines **2201** (e.g., first embedded optical engine **2201A** and the second embedded optical engine **2201B**).

Additionally, while the embodiments are illustrated with a single second semiconductor die **2203**, this is intended to be illustrative and is not intended to be limiting to the embodiments. Rather, any suitable number of second semi-

conductor dies **2203**, such as two or more, may be used. All such number of dies are fully intended to be included within the scope of the embodiments.

According to some embodiments, the sacrificial block **2205** is formed by initially patterning block openings **2209** into but not through a bulk silicon material (e.g., a semiconductor substrate, glass, ceramic, dielectric, bulk semiconductor, silicon wafer, or the like) over a carrier. The block openings **2209** may be formed by acceptable photolithography and etching techniques, such as by forming and patterning a photoresist and then performing an etching process using the patterned photoresist as an etching mask. Once the block openings **2209** have been formed, the photoresist may be removed using a suitable removal process (e.g., ashing).

The patterned bulk silicon material may be singulated into individual sacrificial blocks **2205** by initially transferring the patterned bulk silicon material to a dicing tape. Once transferred to the dicing tape, the patterned bulk silicon may be singulated into a plurality of the sacrificial blocks **2205** using a suitable singulation process such as scribing and breaking, sawing, etching, laser cutting, combinations or the like.

Once singulated, the sacrificial block **2205** is placed with the block openings **2209** facing the first photonic interconnect structure **2100** using, for example, a pick-and-place process. However, any suitable process may be used. According to some embodiments, the sacrificial block **2205** is attached to the first photonic interconnect structure **2100** using an adhesive (e.g., die attach film, light activated adhesive, epoxy, interface materials, combinations, or the like) that is applied to the surface of the sacrificial block **2205** facing the first photonic interconnect structure **2100**. In some embodiments, a first adhesive is a light activated adhesive and is applied in a central region of the surface. According to some embodiments, the light activated adhesive may be activated using a first wavelength of light and may be deactivated using a second wavelength of light. In some embodiments, a second adhesive that is different from the first adhesive is applied along a perimeter of the surface surrounding the first adhesive. In some embodiments, the second adhesive is not a light activated adhesive. In some embodiments, wherein the second adhesive is a light activated adhesive, the second adhesive may be activated using the first wavelength of light but is not deactivated by the second wavelength of light. However, any suitable adhesives or combination of adhesives may be used.

FIG. **23** illustrates a formation of a multiple optical engine device **2300**, according to some embodiments. In particular, FIG. **23** illustrates an encapsulation of the sacrificial block **2205**, the embedded optical engines **2201**, and the second semiconductor die **2203**. The encapsulation may be performed in a molding device (not individually illustrated in FIG. **23**), which may comprise a top molding portion and a bottom molding portion separable from the top molding portion. When the top molding portion is lowered to be adjacent to the bottom molding portion, a molding cavity may be formed for the first photonic interconnect structure **2100**, the sacrificial block **2205**, the embedded optical engines **2201**, and the second semiconductor die **2203**.

During the encapsulation process the top molding portion may be placed adjacent to the bottom molding portion, thereby enclosing the first photonic interconnect structure **2100**, the sacrificial block **2205**, the embedded optical engines **2201**, and the second semiconductor die **2203** within the molding cavity. Once enclosed, the top molding portion and the bottom molding portion may form an airtight

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seal in order to control the influx and outflux of gasses from the molding cavity. Once sealed, an encapsulant **2301** may be placed within the molding cavity. The encapsulant **2301** may be a molding compound resin such as polyimide, PPS, PEEK, PES, a heat resistant crystal resin, combinations of these, or the like. The encapsulant **2301** may be placed within the molding cavity prior to the alignment of the top molding portion and the bottom molding portion, or else may be injected into the molding cavity through an injection port.

Once the encapsulant **2301** has been placed into the molding cavity such that the encapsulant **2301** encapsulates the first photonic interconnect structure **2100**, the sacrificial block **2205**, the embedded optical engines **2201**, and the second semiconductor die **2203**, the encapsulant **2301** may be cured in order to harden the encapsulant **2301** for optimum protection. While the exact curing process is dependent at least in part on the particular material chosen for the encapsulant **2301**, in an embodiment in which molding compound is chosen as the encapsulant **2301**, the curing could occur through a process such as heating the encapsulant **2301** to between about 100° C. and about 130° C., such as about 125° C. for about 60 sec to about 3000 sec, such as about 600 sec. Additionally, initiators and/or catalysts may be included within the encapsulant **2301** to better control the curing process.

However, as one having ordinary skill in the art will recognize, the curing process described above is merely an exemplary process and is not meant to limit the current embodiments. Other curing processes, such as irradiation or even allowing the encapsulant **2301** to harden at ambient temperature, may be used. Any suitable curing process may be used, and all such processes are fully intended to be included within the scope of the embodiments discussed herein.

Once the encapsulant **2301** has been cured, the encapsulant **2301** may be planarized (e.g., chemical mechanical planarization) and a support carrier may be attached to the planar surface of the encapsulant **2301** to provide support during further handling and processing. In an embodiment, the support carrier may be attached using a die attach film, an ultra-violet glue, which loses its adhesive properties when exposed to ultra-violet light. However, other types of adhesives, such as pressure sensitive adhesives, radiation curable adhesives, epoxies, combinations of these, or the like, may also be used. The adhesive may be placed onto the support carrier in a semi-liquid or gel form, which is readily deformable under pressure. Once the support carrier has been attached, the back side of the semiconductor substrate **103A** is thinned and the TSVs **2105** are exposed. The semiconductor substrate **103A** may be thinned by a CMP process, a mechanical grinding, or the like. According to some embodiments, the semiconductor substrate **103A** is thinned to a third height **H3** of between about 25,000 nm and about 100,000 nm. However, any suitable height may be used.

Once the TSVs **2105** have been exposed, the first external contacts **303** may be formed over and in electrical connection with the TSVs **2105**. The first external contacts **303** may be formed over the TSVs **2105** using any of the materials and processes suitable for forming the first external contacts **303** over the first TIVs **111**, as set forth above. Once the first external contacts **303** have been formed, a carrier tape **2307** is attached to the first external contacts **303** and the carrier support is removed to expose the backside of the encapsulant **2301** for further processing.

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FIG. **23** further illustrates a thinning of the encapsulant **2301** in order to expose and/or thin the sacrificial block **2205**, the embedded optical engines **2201**, and the second semiconductor die **2203** for further processing. The thinning may be performed, e.g., using a mechanical grinding or chemical mechanical polishing (CMP) process whereby chemical etchants and abrasives are utilized to react and grind away the encapsulant **2301** until the and the sacrificial block **2205**, the embedded optical engines **2201**, and the second semiconductor die **2203** have been exposed. In some embodiments, the thinning is performed until the block openings **2209** are revealed at the backside of the sacrificial block **2205**. In such embodiments, a block core **2303** is formed between the block openings **2209** and remaining portions of the sacrificial block **2205** form sidewalls of a vertical fiber attachment unit **2305**. As such, the sacrificial block **2205**, the embedded optical engines **2201**, and the second semiconductor die **2203** may have a planar surface that is also coplanar with the encapsulant **2301**.

However, while the CMP process described above is presented as one illustrative embodiment, it is not intended to be limiting to the embodiments. Any other suitable removal process may be used to thin the encapsulant **2301** and the sacrificial block **2205** and expose the block openings **2209**. For example, a series of chemical etches may be utilized. This process and any other suitable process may be utilized to thin the encapsulant **2301** and the sacrificial block **2205**, and all such processes are fully intended to be included within the scope of the embodiments.

FIG. **24** illustrates the seventh package assembly **2400** comprising the multiple optical engine device **2300**, according to some embodiments. In particular, FIG. **24** illustrates a mounting of the multiple optical engine device **2300** to the package substrate **407**, a removal of the block core **2303**, and attachment of a first optical fiber **2401** and a second optical fiber **2403**, according to some embodiments.

The multiple optical engine device **2300** may be removed from the carrier tape **2307** and placed over the package substrate **407** using, for example, a pick-and-place process. Once placed, the multiple optical engine device **2300** may be mounted to the package substrate **407** for example by performing a suitable bonding process such as a solder reflow process to bond the first external contacts **303** of the multiple optical engine device **2300** to conductive contacts of the package substrate **407**. However, any suitable bonding process may be utilized.

Once mounted to the package substrate **407**, the block core **2303** may be removed from the sacrificial block **2205**. In embodiments wherein the sacrificial block **2205** is attached using a first adhesive that is light activated, the block core **2303** may be removed by deactivating the adhesive using a light source of the first wavelength, as described above. As such, the block core **2303** is released from the first photonic interconnect structure **2100** and may be removed using, for example, a pick-and-place process. However, any suitable removal process may also be used.

Once the block core **2303** has been removed, a cavity is formed within the vertical fiber attachment unit **2305** and the first optical fiber **2401** may be attached to the multiple optical engine device **2300**. According to some embodiments, the first optical fiber **2401** may be a power optical fiber and may be inserted into the cavity of the vertical fiber attachment unit **2305** in a location over the first waveguides **105** and/or first photonic components **107**. According to some embodiments, sidewalls of the vertical fiber attachment unit **2305** secure the first optical fiber **2401** in a vertical position, for example, by a frictional force. In some embodi-

ments, an optical adhesive (e.g., optically clear glue) transparent to the relevant wavelengths of light may be used to secure the first optical fiber **2401** within the vertical fiber attachment unit **2305**.

In some embodiments, the second optical fiber **2403** may be attached to the optional interfacial layer **2207** of an optical engine (e.g., the second embedded optical engine **2201B**). According to some embodiments, the optional interfacial layer **2207** is a light activated adhesive film. In such embodiments, the second optical fiber **2403** may be a signal optical fiber and may be attached to the optional interfacial layer **2207** by projecting a source light of an activation wavelength of the light activated adhesive film. In some embodiments, an optical adhesive transparent to the relevant wavelengths of light may be used to secure the second optical fiber **2403** to the optional interfacial layer **2207** or the backside of the second embedded optical engine **2201B**. In other embodiments, a second fiber attachment unit (not shown) may be used to attach the second optical fiber **2403**.

FIG. **24** further illustrates that, during operation, the embedded optical engines **2201** and the second semiconductor die **2203** may receive electrical power and/or electrical communications via the package substrate **407** as indicated by the first directional arrows **905**. In addition, the embedded optical engines **2201** and the first optical fiber **2401** and the second optical fiber **2403** may optically communicate during operation as indicated by the second directional arrows **2405**.

The first waveguides **105** and the first photonic components **107** of the first photonic interconnect structure **2100** are utilized to transmit and receive optical signals between the first optical fiber **2401** (e.g., power fiber) and the embedded optical engines **2201**. In particular, the first photonic components **107** of the first photonic interconnect structure **2100** converts electrical signals to optical signals for transmission along the first optical fiber **2401**, and convert optical signals from the first optical fiber **2401** to electrical signals. Accordingly, the first photonic components **107** of the first photonic interconnect structure **2100** are responsible for the input/output (I/O) of optical signals to/from the first optical fiber **2401**. In some embodiments, the first photonic components **107** of the first photonic interconnect structure **2100** may be used to exchange optical communications between the **2201A** and **2201B**, for example, in die-to-die communication. According to some embodiments, the second semiconductor die **2203** may be, for example, a multi-die switch that controls the flow of optical communications and electrical communications of the embedded optical engines **2201**.

The first waveguides **105** and the first photonic components **107** of the second embedded optical engine **2201B** are utilized to transmit and receive optical signals between the second optical fiber **2403** (e.g., signal fiber) and the first photonic interconnect structure **2100**. In particular, the first photonic components **107** of the second embedded optical engine **2201B** convert electrical signals to optical signals for transmission along the second optical fiber **2403**, and convert optical signals from the second optical fiber **2403** to electrical signals. Accordingly, the first photonic components **107** of the second embedded optical engine **2201B** is responsible for the input/output (I/O) of optical signals to/from the second optical fiber **2403**.

FIG. **25** illustrates another embodiment of an eighth package assembly **2500**, according to some embodiments. The eighth package assembly **2500** is similar to the seventh package assembly **2400** of FIG. **24** except that the eighth

package assembly **2500** also includes first optical engines **300** comprising an optional front-side (FS) Mirror ARC **2501**, and an optional backside (BS) Mirror ARC **2503**, index-matching glue **2505** and a second photonic interconnect structure **2507** comprising the second waveguide material layer **1201**.

According to some embodiments, the second photonic interconnect structure **2501** is formed with the second waveguide material layer **1201** (e.g., silicon nitride) between the buried oxide layer **103B** and the semiconductor substrate **103A**. However, any suitable material may be used for the second waveguide material layer **1201**.

The first optical engines **300** may be formed with the optional backside (BS) Mirror ARC **2503** by initially depositing and patterning the ARC material on the semiconductor substrate **103A** prior to forming the buried oxide layer **103B**, as described above. The ARC material may be an anti-reflective film such as single layer ARC and/or double layer ARC materials (e.g., aluminum oxide, titanium oxide, silicon oxide, combinations, or the like). However, any suitable anti-reflective material may be used. Once deposited, the optional backside (BS) Mirror ARC **2503** may be patterned using, e.g., a photolithographic masking and etching process, whereby a photoresist is placed, exposed, and developed, and the photoresist is then used as a mask during an anisotropic etching process. However, any suitable process for patterning the optional backside (BS) Mirror ARC **2503** may be utilized.

The first optical engines **300** may be formed with the optional front-side (FS) Mirror ARC **2501** by initially depositing and patterning the ARC material over the first waveguides **105** and/or the first photonic components **107** prior to forming the gap-fill material **127**, as described above. The optional front-side (FS) Mirror ARC **2501** may be formed using any of the materials and processes suitable for forming the optional backside (BS) Mirror ARC **2503**.

The index-matching glue **2505** may be used to attach the first optical engines **300** to the second photonic interconnect structure **2507**. The index-matching glue **2505** may be, for example, an optically clear adhesive (OCA) optical resins, optical glass, optical ceramics, combinations, or the like) and matches an index of the first backfill structure **301**. The index-matching glue **2505** may be applied in any suitable form (e.g., liquid, film, tape, or the like) using a suitable process (e.g., adhesive dispenser, printer, or the like). During operation, the index-matching glue **2505** is used to conduct optical communications between the first optical engines **300** and the waveguides of the second photonic interconnect structure **2507**, as indicated by the third directional arrows **2509**.

FIG. **25** further illustrates an encapsulation of the first optical engines **300**, the second semiconductor die **2203** (e.g., ASIC, Switch, or the like), and the first waveguides **105** over the second photonic interconnect structure **2507**, according to some embodiments. The encapsulant **2301** may be formed using any of the materials and techniques, as set forth above. In some embodiments, the first waveguides **105** remain exposed at a perimeter of the second photonic interconnect structure **2507**. Once the encapsulant **2301** has been formed, the second photonic interconnect structure **2507** may be mounted to the package substrate **407** using the first external contacts **303**, as set forth above. Once mounted, the first underfill **409** may be formed between the second photonic interconnect structure **2507** and the package substrate **407**. The signal fibers **2403** may be attached to the backsides of the **300** and the power fibers **2401** may be attached to the exposed surfaces of the first waveguides **105**.

According to some embodiments, the signal fibers **2403** and the power fibers **2401** may be attached using an optical adhesive. In other embodiments (not specifically illustrated), backside cavities may be formed through the encapsulant **2301** by forming the vertical fiber attachment units **2305** used to secure the power fibers **2401**, as set forth above. However, any suitable materials and techniques may be used to attach signal fibers **2403** and/or the power fibers **2401**.

FIG. **26** illustrates a formation of a ninth package assembly **2600**, according to still further embodiments. Two optical engines **300A** and **300B** (see FIG. **3**) are mounted to a third photonic interconnect structure **2601** and optically communicate via an embedded Si waveguide **2607**. The optical engines **300A** and **300B** are electrically connected to and controlled by the second semiconductor dies **2203A** and **2203B** (e.g., Host ASICs) through the third photonic interconnect structure **2601**, respectively.

According to some embodiments, the third photonic interconnect structure **2601** is formed by initially forming conductive pillars **2605** (e.g., Cu pillars) and then placing or forming an embedded Si waveguide **2607** (e.g., photonic die **117** and first waveguide **105** of FIG. **3**) on a carrier substrate (not separately illustrated). An encapsulant **2301** (e.g., molding compound) may be formed or placed over the conductive pillars **2605** and the embedded Si waveguide **2607**, using any of the encapsulation materials and techniques set forth above. Once encapsulated, a chemical mechanical planarization (CMP) process may be performed to thin the embedded Si waveguide **2607** and encapsulant **2301**, leaving behind the silicon waveguide and any other desired structures such as grating couplers and to expose the conductive pillars **2605**. As such, the embedded Si waveguide **2607** and the conductive pillars **2605** may have a planar surface that is also coplanar with the encapsulant **2301**.

FIG. **26** further illustrates the formation of the front side redistribution structure **1609** over the embedded Si waveguide **2607**, the conductive pillars **2605**, and the encapsulant **2301**, according to some embodiments. The front side redistribution structure **1609** may be formed using any of the materials and processes described above and may be formed with any desired number of the front side dielectric layers **1611** and the front side redistribution layers **1613**.

Once the front side redistribution structure **1609** has been formed, a second carrier may be applied to the exposed surface of the front side redistribution structure **1609** and the first carrier is removed. Once the first carrier has been removed, a backside redistribution structure **1801** may be formed over the embedded Si waveguide **2607**, the conductive pillars **2605**, and the encapsulant **2301**, according to some embodiments.

FIG. **26** further illustrates a formation of first optical through vias (OTV) **2609A** optically coupling the embedded Si waveguide **2607** through the backside redistribution structure **1801** and second optical through vias **2609B** optically coupling the first optical through vias **2609A** to subsequently placed first optical engines **300**. The first optical through vias **2609A** and second optical through vias **2609B** may be collectively referred to herein as the optical through vias **2609**. The optical through vias **2609** may be formed by initially forming openings through the backside dielectric layers **1803** and exposing the embedded Si waveguide **2607** in locations over the grating couplers **106A**.

According to some embodiments, an optical fill material (e.g., index-matching polymer) is deposited within the openings and then hardened, for example, using an anneal process to form the first optical through vias **2609A**. Once the first optical through vias **2609A** have been formed, the

second optical through vias **2609B** may be formed over the backside redistribution structure **1801** by initially depositing and patterning a photoresist and using the patterned photoresist as a mask. A second optical fill material (e.g., index-matching underfill) may be deposited in the openings and then hardened to form the second optical through vias **2609B**, according to some embodiments. Once formed, the photoresist is removed in a process such as ashing. The optical through vias **2609** may be formed using any of the materials and techniques suitable for forming the index-matching glue **2505** and/or the optical windows **2103**, as set forth above.

Once formed, the second optical through vias **2609B** and the second external contacts **417** may be used to mount the first optical engines **300A** and **300B** to the backside redistribution structure **1801**, according to some embodiments. In some embodiments, the first backfill structures **301** may be attached to the second optical through vias **2609B** using an adhesive film and the second external contacts **417** may be attached to contact pads of the **1801** using, for example, a solder reflow process. However, any suitable connectors and mounting techniques may be used. According to some embodiments, the second semiconductor dies **2203A** and **2203B** may be mounted to the backside redistribution structure **1801** using the first external contacts **303**. However, any suitable connectors and mounting techniques may be used.

During operation, the first optical through vias **2609A** are used to conduct optical communications between the first optical engines **300** and the embedded Si waveguide **2607** (e.g., die-to-die optical communications), as indicated by the fourth directional arrows **2611**. The second semiconductor dies **2203A** and **2203B** may electrically communicate to one another and/or to the first optical engines **300A** and **300B** through the third photonic interconnect structure **2601**.

FIG. **26** further illustrates mounting of the third photonic interconnect structure **2601** to an optional interposer **2603** using the first external contacts **303**, for example, between the formation of the first optical through vias **2609A** and the formation of the second optical through vias **2609B**. According to some embodiments, the optional interposer **2603** comprises second external contacts **2613** for external connection to the ninth package assembly **2600**. In some embodiments, the second external contacts **2613** are formed as solder balls. However, any suitable contacts may be used.

By utilizing the methods and structures presented herein, more economical manufacturing processes may be utilized to help prevent optical losses with edge couplers for photonic optical engines. In particular, optical losses due to light beams overlapping with substrate materials (e.g., silicon) may be reduced.

In accordance with some embodiments, a method includes: providing a first layer between a second layer and a semiconductor substrate; forming a first waveguide in the second layer; forming a photonic die over the first waveguide; forming a first cavity in the semiconductor substrate and exposing the first layer; filling the first cavity with a first backfill material; and electrically coupling an electronic die to the photonic die. In an embodiment the method further includes forming a second cavity in the semiconductor substrate and exposing the first layer; and filling the second cavity with a second backfill material, the second backfill material being different from the first backfill material. In an embodiment the method further includes forming through insulator vias in the semiconductor substrate prior to the forming the first cavity. In an embodiment the method further includes electrically connecting the through insulator vias to a package substrate. In an embodiment the electri-

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cally coupling the electronic die to the photonic die comprises hybrid bonding the electronic die to the photonic die. In an embodiment the method further includes mounting the electronic die adjacent the semiconductor substrate and electrically coupling the electronic die to the through insulator vias. In an embodiment the first layer comprises silicon oxide.

In accordance with another embodiment, a method includes: forming a first waveguide adjacent to a first oxide layer; forming a photonic die adjacent and optically coupled to the first waveguide; hybrid bonding an electronic die to the photonic die; and forming a second waveguide adjacent the first oxide layer opposite the first waveguide, the second waveguide being optically coupled to the first waveguide through the first oxide layer. In an embodiment the method further includes, prior to forming the second waveguide, encapsulating the photonic die, the electronic die and a through molding via in an encapsulant, wherein the forming the second waveguide forms the second waveguide with a polymer material. In an embodiment forming the second waveguide comprises forming part of the second waveguide adjacent the encapsulant. In an embodiment the method further includes forming a first redistribution structure over the second waveguide. In an embodiment the method further includes forming a second redistribution structure adjacent and electrically coupled to the through molding via. In an embodiment the method further includes: forming the second waveguide using a nitride material; forming a second oxide layer over the second waveguide; and forming a conductive via through the second oxide layer, the second waveguide, and the first oxide layer, the conductive via being electrically coupled to the photonic die. In an embodiment the method further includes, prior to the forming the conductive via, forming a third waveguide over the second oxide layer using a silicon nitride material, the third waveguide being optically coupled to the second waveguide.

In accordance with yet another embodiment, a semiconductor device includes: a first oxide substrate structure adjacent a semiconductor substrate; an oxide layer over the semiconductor substrate and the first oxide substrate structure; a first waveguide over the oxide layer; a photonic die over the oxide layer and optically coupled to the first waveguide; and an electronic die electrically coupled to the photonic die. In an embodiment the first waveguide comprises a silicon tip, wherein the silicon tip and the first oxide substrate are coterminous with a sidewall of the semiconductor device. In an embodiment first die contacts of the electronic die are bonded to second die contacts of the photonic die. In an embodiment the semiconductor device further includes a through insulator via extending through the oxide layer and the semiconductor substrate, the through insulator via electrically coupling the photonic die to the electronic die. In an embodiment the semiconductor device further includes a second oxide substrate structure extending through the semiconductor substrate, wherein the first oxide substrate comprises a first material and the second oxide substrate structure comprises a second material that is different from the first material. In an embodiment the semiconductor device further includes: a package substrate; a through insulator via through the oxide layer and the semiconductor substrate, the through insulator via being electrically coupled to the photonic die; and an external contact electrically coupling the through insulator via to the package substrate, wherein the electronic die is mounted to the package substrate and the electronic die is electrically coupled to the photonic die by the package substrate.

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The foregoing outlines features of several embodiments so that those skilled in the art may better understand the aspects of the present disclosure. Those skilled in the art should appreciate that they may readily use the present disclosure as a basis for designing or modifying other processes and structures for carrying out the same purposes and/or achieving the same advantages of the embodiments introduced herein. Those skilled in the art should also realize that such equivalent constructions do not depart from the spirit and scope of the present disclosure, and that they may make various changes, substitutions, and alterations herein without departing from the spirit and scope of the present disclosure.

What is claimed is:

1. A semiconductor device, comprising:
 - a first oxide substrate structure adjacent a semiconductor substrate along a first direction, a first surface of the first oxide substrate structure facing a second direction different than the first direction, a first surface of the semiconductor substrate facing the second direction; an oxide layer over the first surface of the semiconductor substrate along the second direction and the first surface of the first oxide substrate structure along the second direction;
 - a first waveguide over the oxide layer;
 - a photonic die over the oxide layer and optically coupled to the first waveguide; and
 - an electronic die electrically coupled to the photonic die.
2. The semiconductor device of claim 1, wherein the first waveguide comprises a silicon tip, wherein the silicon tip and the first oxide substrate structure are coterminous.
3. The semiconductor device of claim 1, wherein first die contacts of the electronic die are bonded to second die contacts of the photonic die.
4. The semiconductor device of claim 1, further comprising a through insulator via extending through the oxide layer and the semiconductor substrate, the through insulator via electrically coupling the photonic die to the electronic die.
5. The semiconductor device of claim 4, further comprising a second oxide substrate structure extending through the semiconductor substrate, wherein the first oxide substrate structure comprises a first material and the second oxide substrate structure comprises a second material that is different from the first material.
6. The semiconductor device of claim 1, further comprising:
 - a package substrate;
 - a through insulator via extending through the oxide layer and the semiconductor substrate, the through insulator via being electrically coupled to the photonic die; and
 - an external contact electrically coupling the through insulator via to the package substrate, wherein the electronic die is mounted to the package substrate and the electronic die is electrically coupled to the photonic die by the package substrate.
7. A semiconductor device, comprising:
 - a semiconductor substrate, the semiconductor substrate having a first surface and a second surface opposite the first surface;
 - a first layer over the first surface of the semiconductor substrate;
 - a second layer over the first layer, wherein the first layer is between the second layer and the semiconductor substrate;
 - a first dielectric fill structure in a first cavity in the semiconductor substrate, the first dielectric fill structure extending from the second surface of the semiconductor

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- tor substrate to the first layer, wherein all surfaces of the second layer are free from contact with the first dielectric fill structure;
- a first waveguide in the second layer;
- a photonic die over the first waveguide, wherein the first layer and the second layer are between the photonic die and the semiconductor substrate; and
- an electronic die bonded to the photonic die, wherein the photonic die is between the electronic die and the semiconductor substrate.
8. The semiconductor device of claim 7, further comprising:
- a second dielectric fill structure in a second cavity in the semiconductor substrate, the second dielectric fill structure extending from the second surface of the semiconductor substrate to the first layer.
9. The semiconductor device of claim 7, further comprising:
- through vias in the semiconductor substrate, wherein the through vias are conductive.
10. The semiconductor device of claim 9, further comprising:
- a package substrate attached to the semiconductor substrate, wherein the package substrate comprises conductive features electrically coupled to corresponding ones of the through vias.
11. The semiconductor device of claim 9, wherein the electronic die is bonded to the photonic die with dielectric-to-dielectric and metal-to-metal bonds.
12. The semiconductor device of claim 9, wherein the first layer comprises a silicon oxide layer.
13. The semiconductor device of claim 9, wherein the second layer comprises a silicon layer.
14. A semiconductor device, comprising:
- a first substrate, the first substrate comprising:
- a first silicon layer,
- a dielectric fill adjacent the first silicon layer,
- an insulating layer over the first silicon layer and the dielectric fill, and

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- a second silicon layer over the insulating layer, the second silicon layer comprising a first waveguide, the first waveguide overlapping the dielectric fill along a line perpendicular to a major surface of the first silicon layer;
- a passivation layer over the second silicon layer;
- a photonic die over the passivation layer; and
- an electronic die attached to the photonic die.
15. The semiconductor device of claim 14, further comprising:
- a package substrate attached to the first substrate.
16. The semiconductor device of claim 15, further comprising:
- a spacer between the package substrate and the first substrate.
17. The semiconductor device of claim 15, further comprising:
- a first fiber attachment housing attached to the package substrate, wherein the first fiber attachment housing comprises an optical fiber, wherein the optical fiber is aligned with the first waveguide.
18. The semiconductor device of claim 17, wherein the first fiber attachment housing is attached to the package substrate with a transparent adhesive, wherein the transparent adhesive extends between the first fiber attachment housing and the first substrate.
19. The semiconductor device of claim 17, further comprising:
- an encapsulant along sidewalls of the electronic die; and
- a support substrate over the electronic die and the encapsulant, the support substrate having an alignment tab, wherein the first fiber attachment housing comprises an alignment notch, wherein the alignment tab is aligned to the alignment notch.
20. The semiconductor device of claim 17, wherein the optical fiber overlaps the dielectric fill.

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